

積體電路設計導論

Laker Tutorial

Date: 2022/10/04

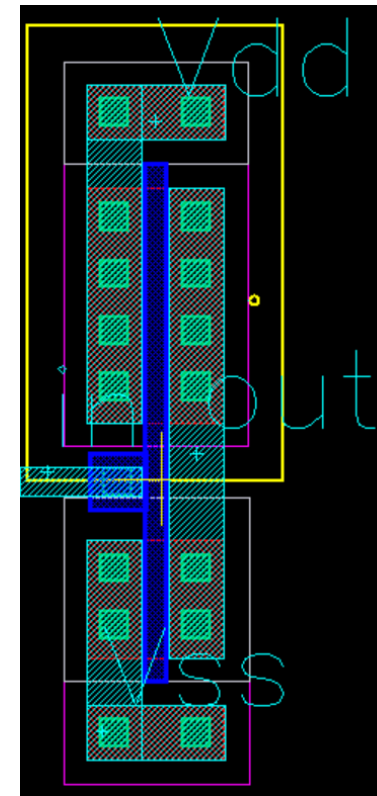
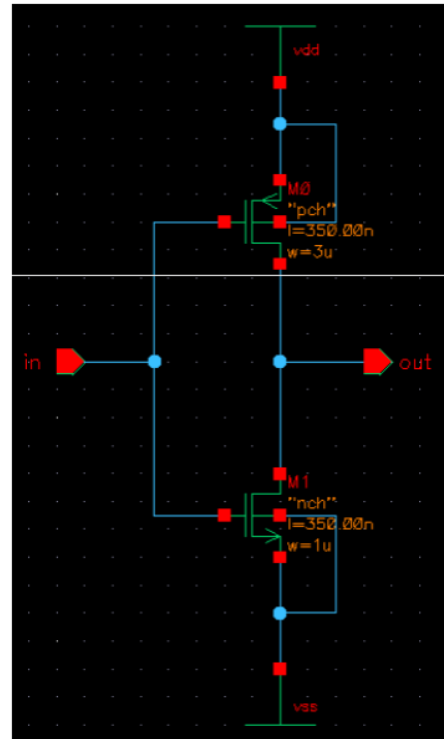
Presenter: Andrew Lee, Yu-Cheng Hong

Outline

- ❑ What is Laker?
- ❑ File Requirement
- ❑ Environment Setting
- ❑ Hot Key
- ❑ Process v.s. Layout
- ❑ Multiply the Width
- ❑ Calibre DRC Flow
- ❑ Calibre LVS Flow
- ❑ Export / Import Design

What is Laker?

- ❑ **Laker** is a tool which enable user to generate layout results so that we can ask the Fab (Ex: TSMC) to make a Custom IC.



File Requirement

File Requirement

☐ Netlist : *.spi

- The *.spi file you want to transfer to layout

☐ Technology file : laker.tf

- The process information (EX: 0.18u, 65nm, 28nm ...)

☐ DRC file : rule.drc

- To check if the layout violates fabrication rule

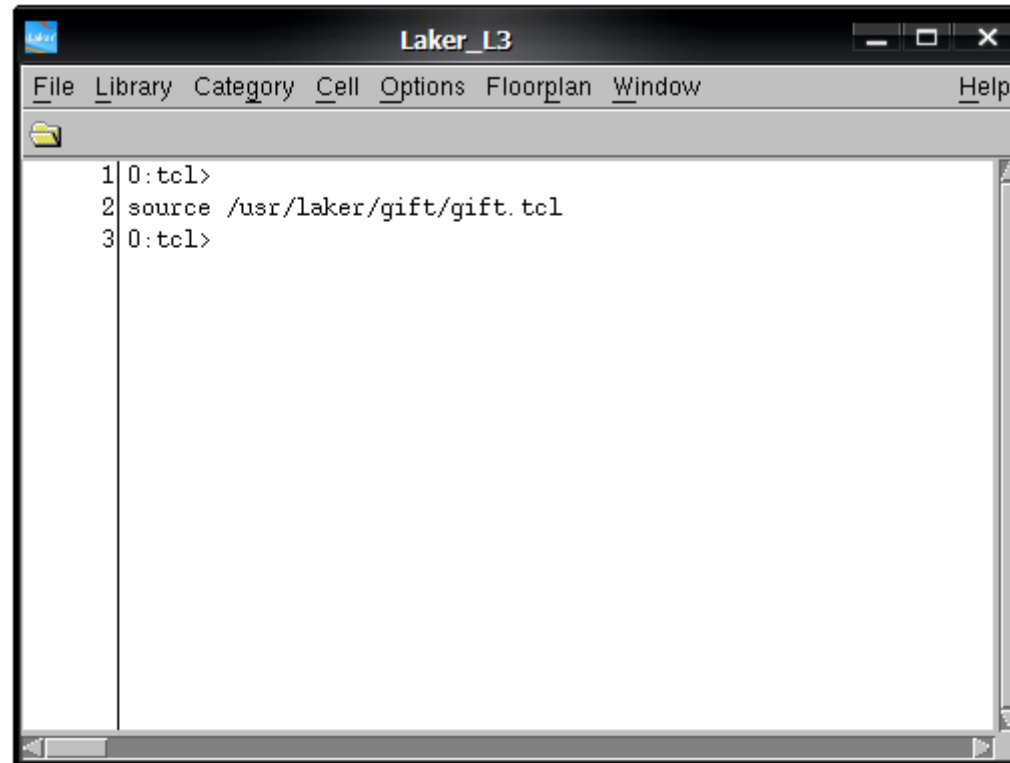
☐ LVS file : Rule.lvs

- To check whether layout and schematic are the same

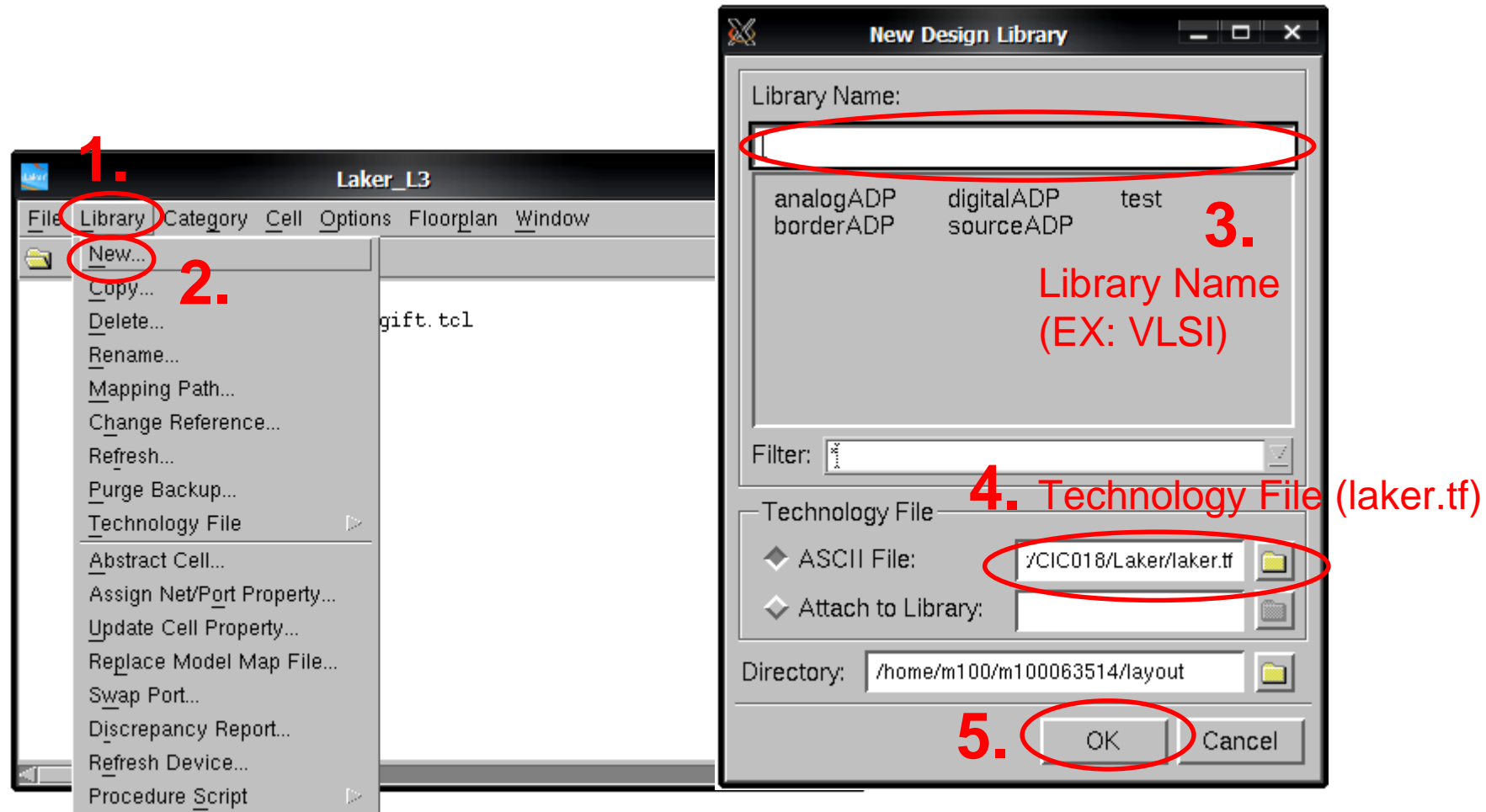
Environment Setting

Laker - Initialize

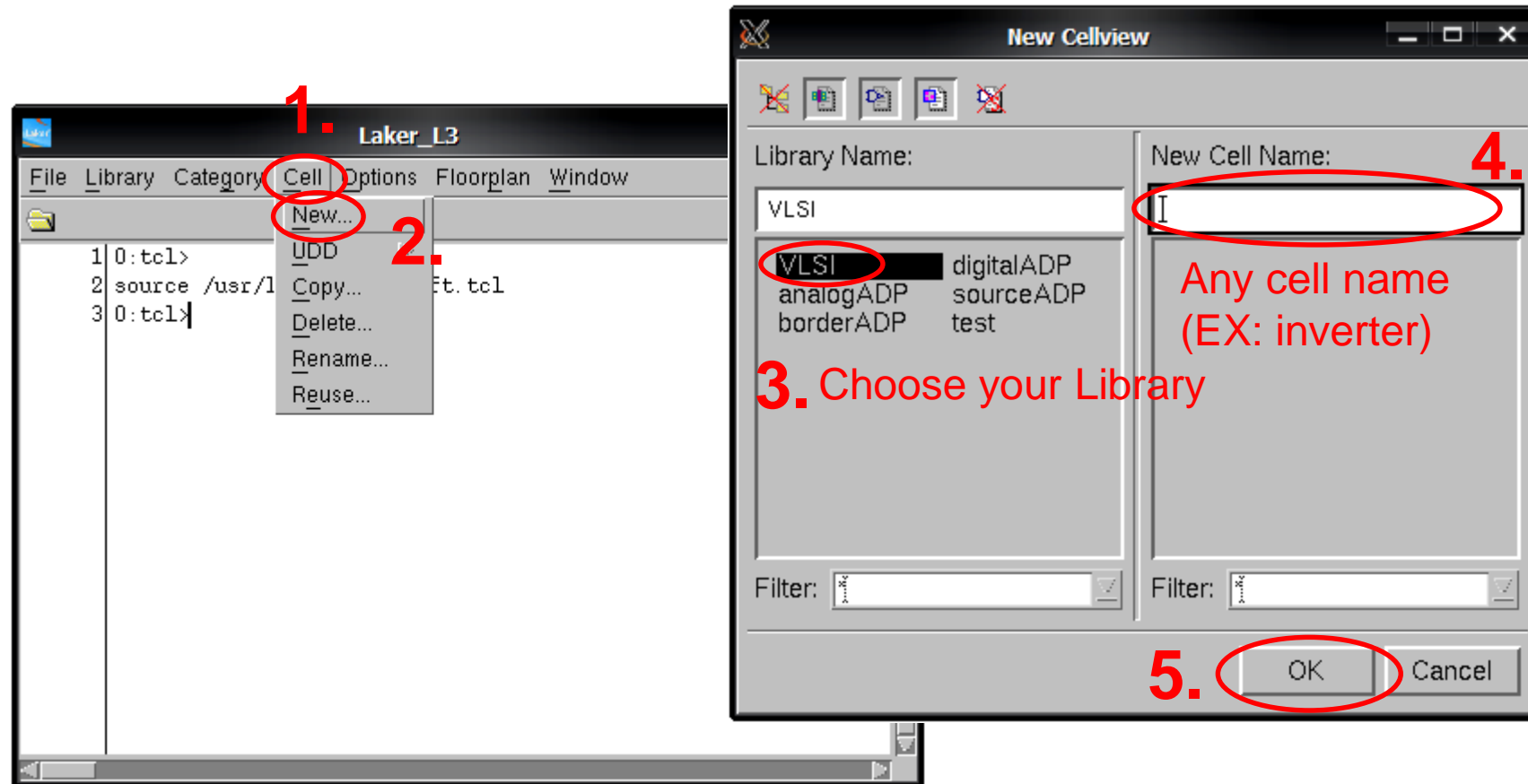
- ❑ source /usr/cadtool/user_setup/08-laker.csh
- ❑ Create a layout directory by “mkdir ”
- ❑ Type the command “laker &” in terminal
- ❑ Main Window



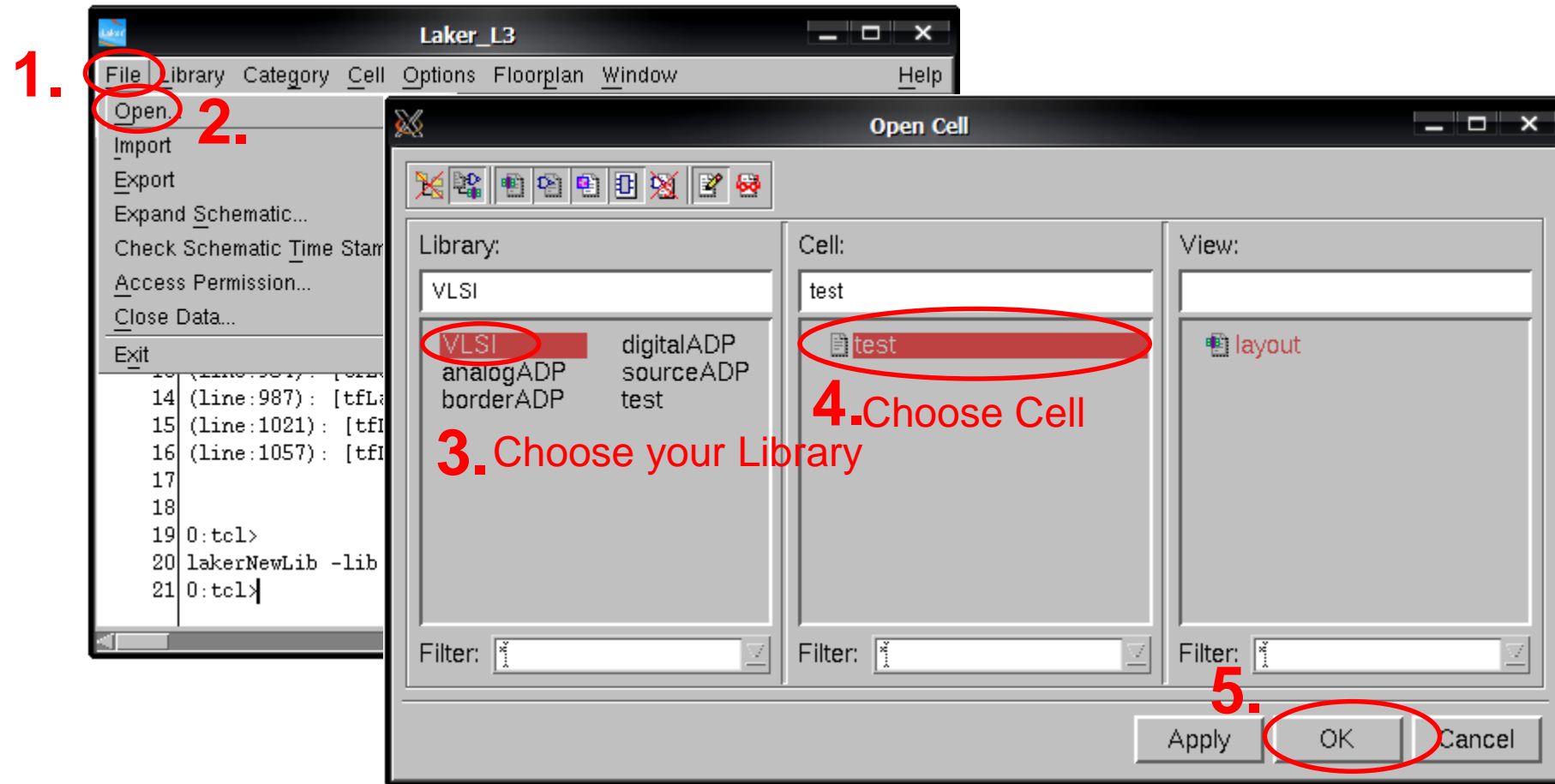
Laker – Create New Library



Laker – Create New Cell

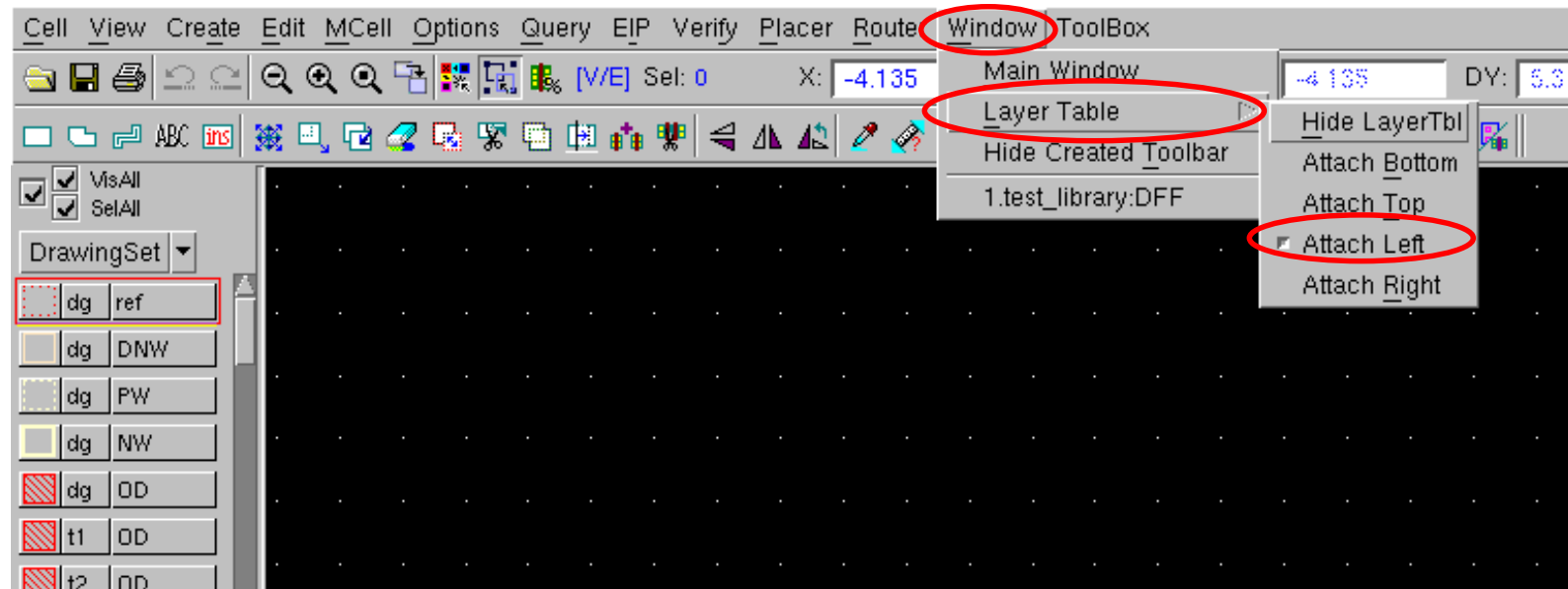


Laker – Open Cell



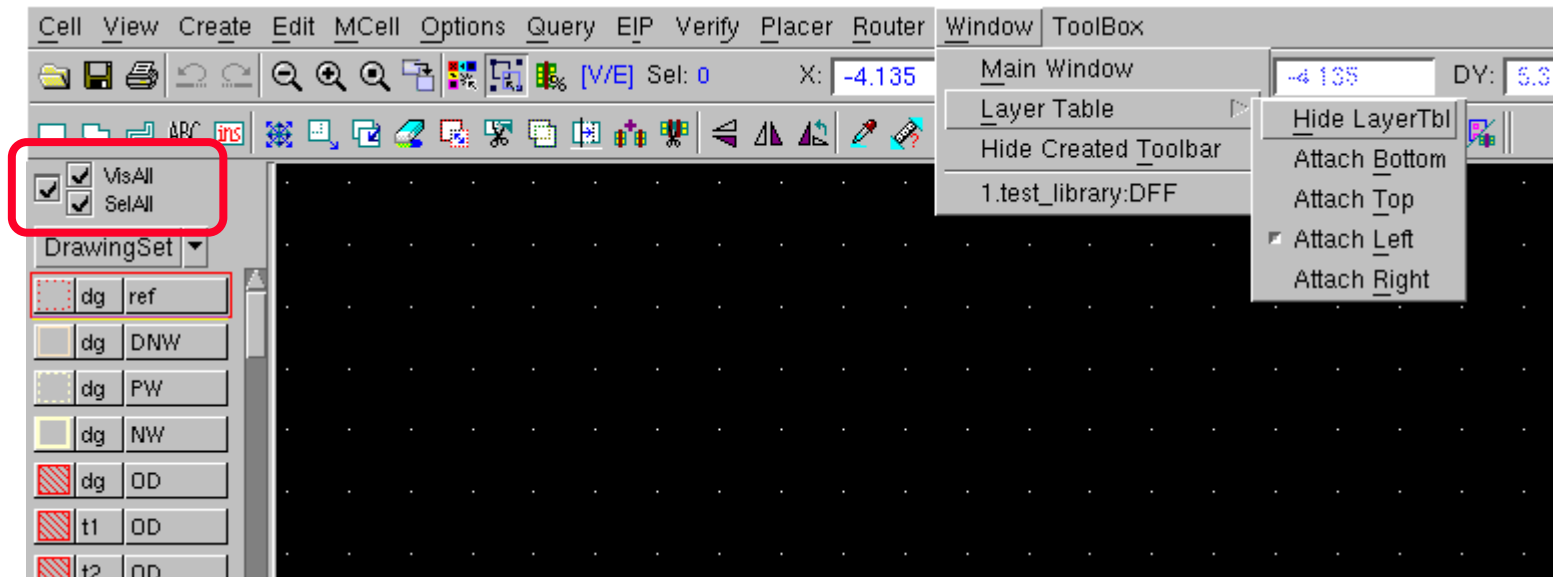
Laker – Editor

- ❑ Window → Layer Table → Attach Left
 - Don't select “Hide Created ToolBar”



Laker – Editor

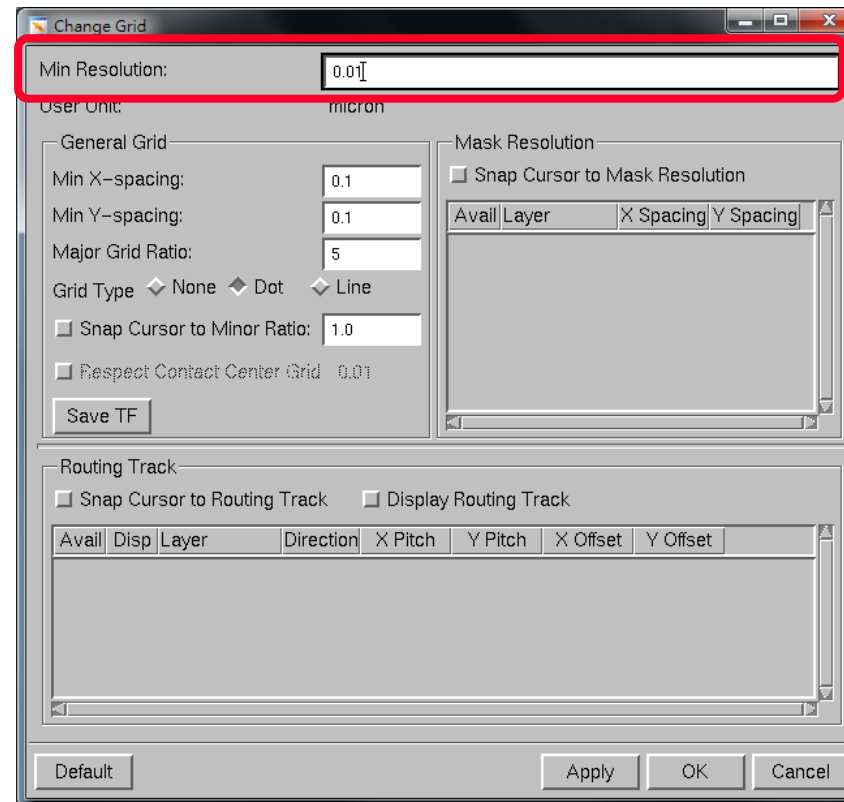
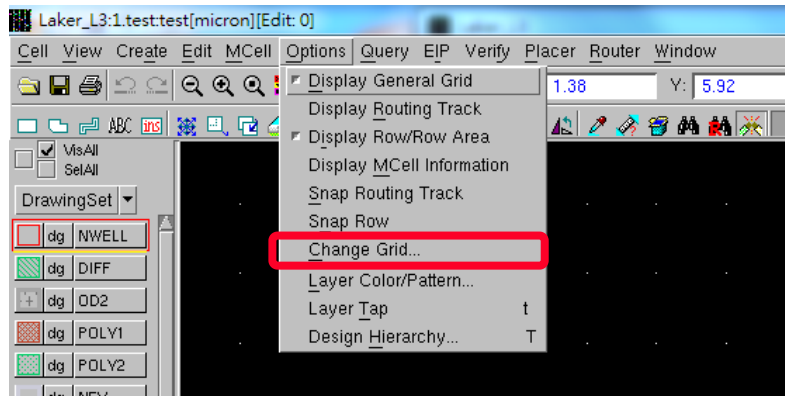
- ❑ Selectable and Visible
 - Visible : You can see those materials
 - Selectable : You can use those materials



Laker – Grid

❑ Change Resolution

- Check at “Option → Change Grid”
- Min Resolution = 0.01



Hot Key

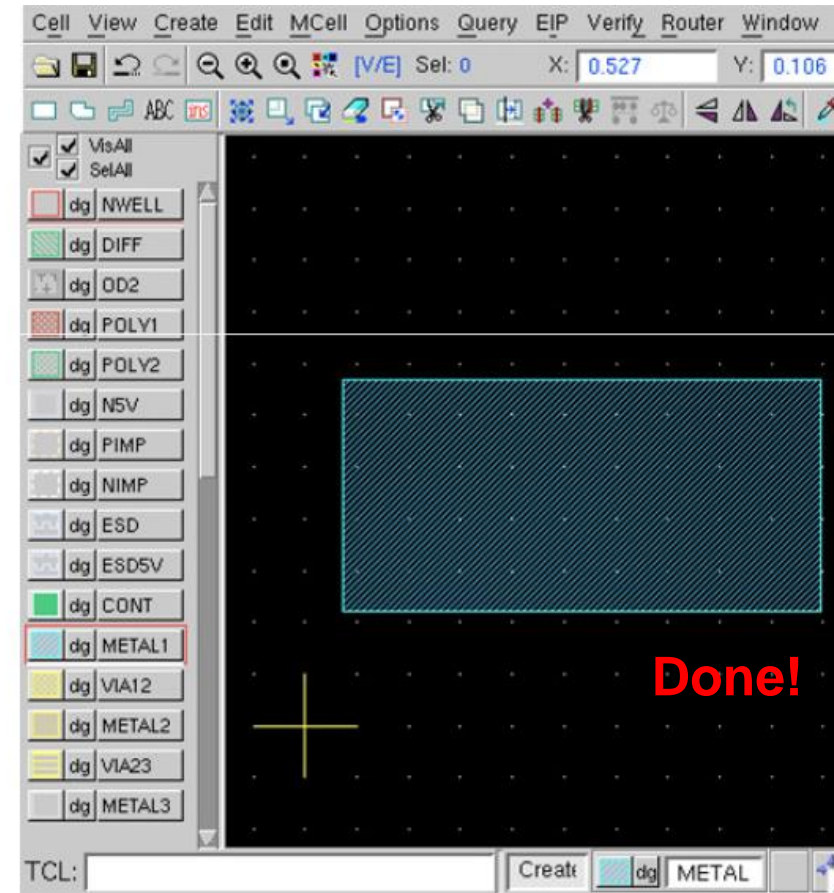
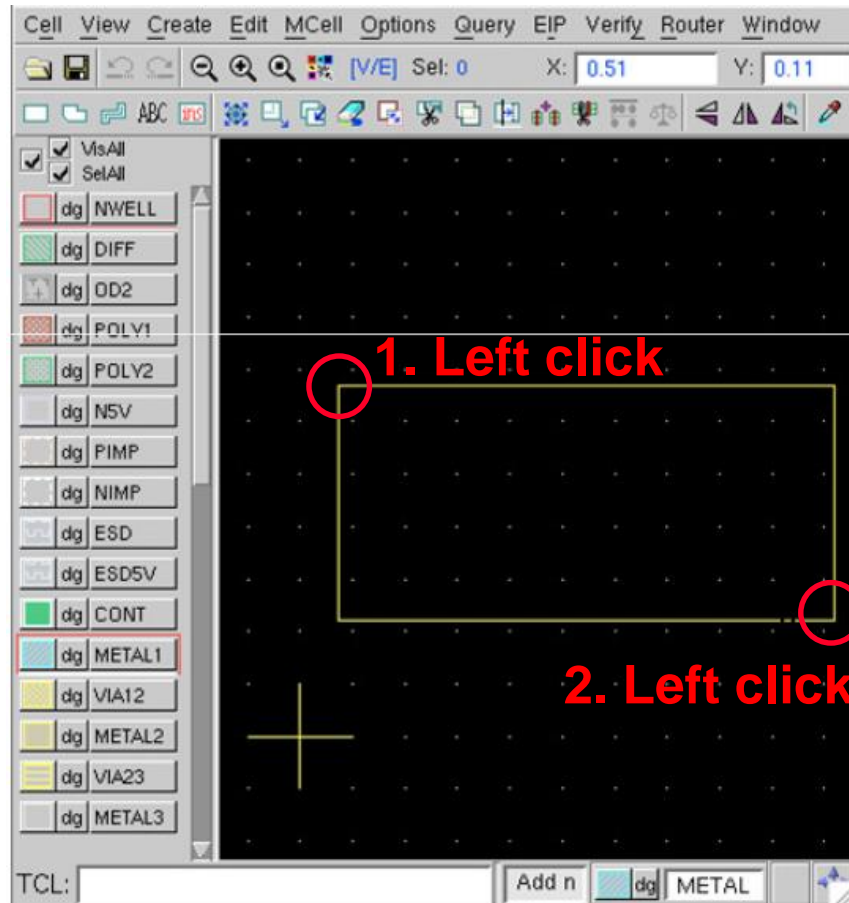
Laker – Hot Key Table

Hot Keys	Attitude	Hot Keys	Attitude
R	Rectangular	P	Path
S	Stretch	Z	Zoom area
M	Move	ctrl/shift+z	zoom in/out
C	Copy	D	Distance
Del	Delete	K/shift+K	Marker / Remove all Markers
Q	Quality	I	Instance
Esc	Release attitudes	A	Align
u/shift+u	Undo / redo		

Laker – (R)ectangular

❑ Draw Rectangular (R)

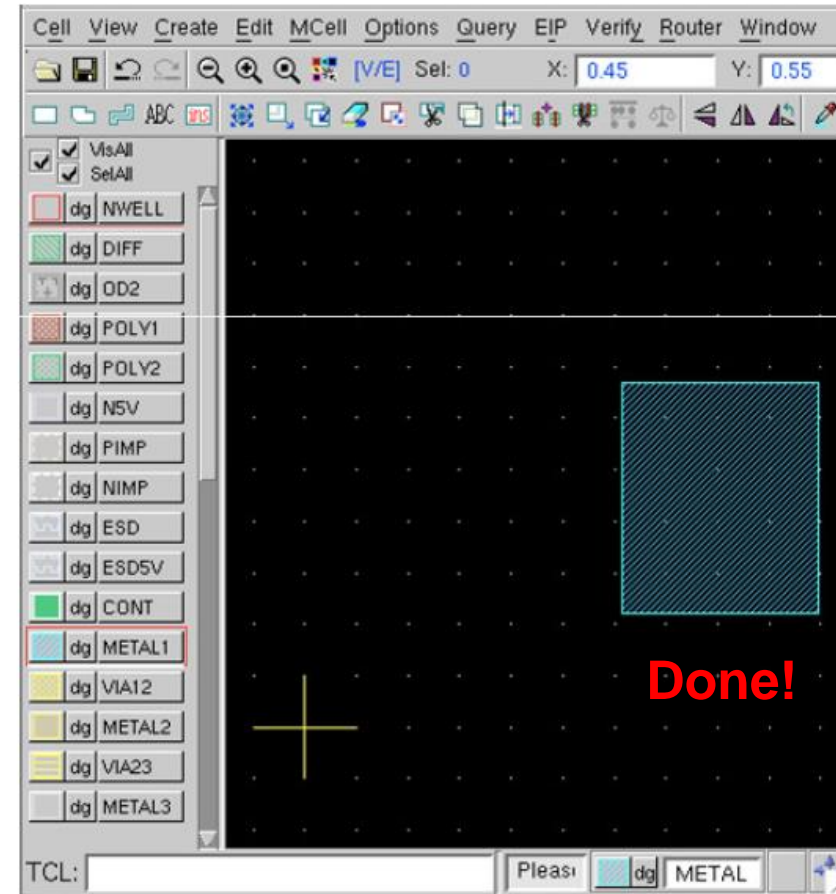
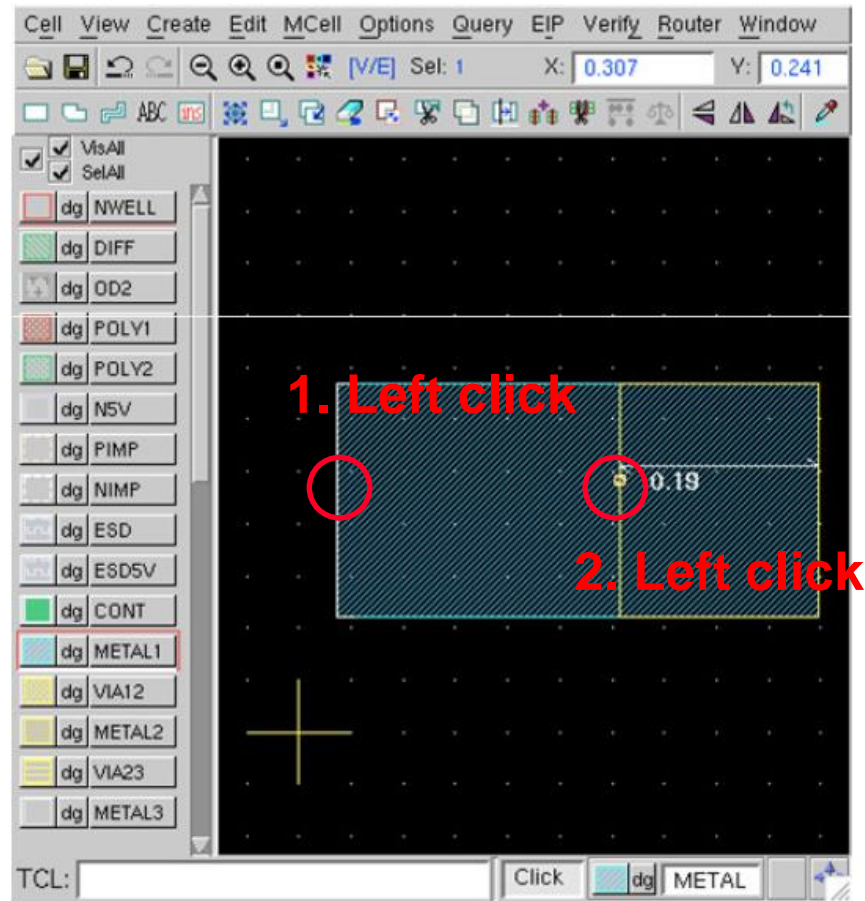
- Choose a material → Press r → point ref. → point dest.



Laker – (S)tretch

□ Stretch (s)

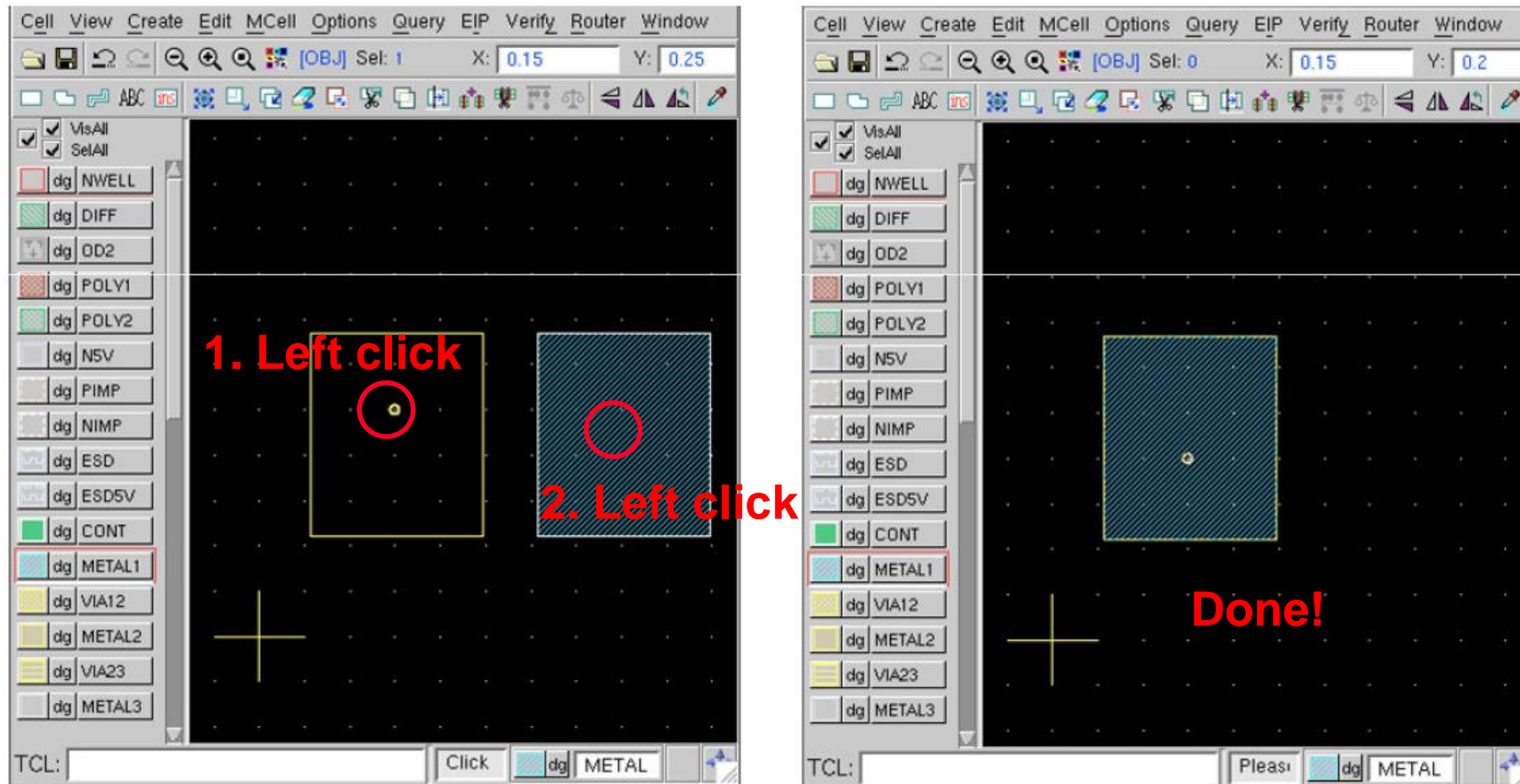
- Press s → select edge → point ref. → point dest.



Laker – (M)ove

❑ Move (m)

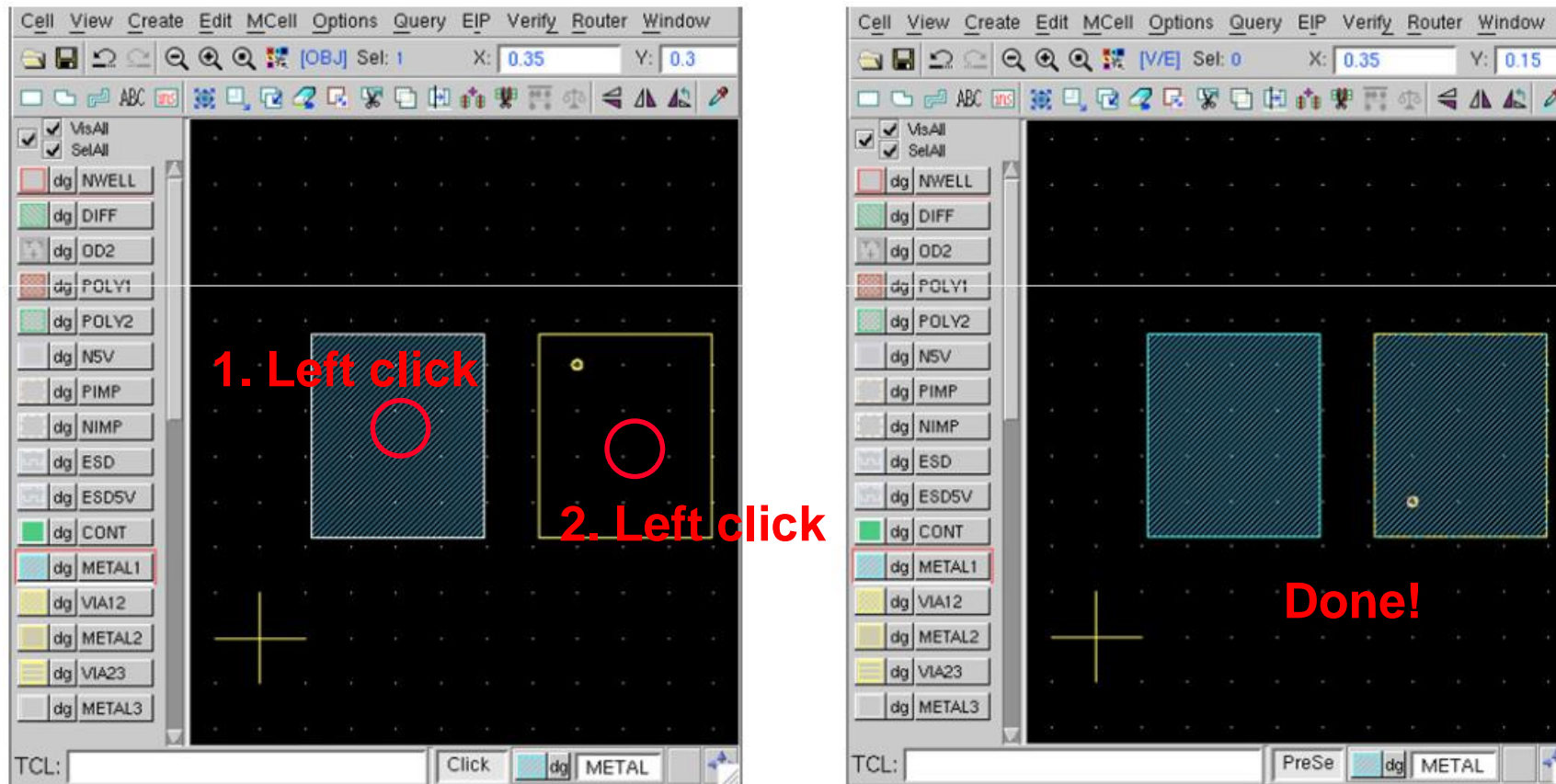
- Press m → select figure → point ref. → point dest.



Laker – (C)opy

❑ Copy (c)

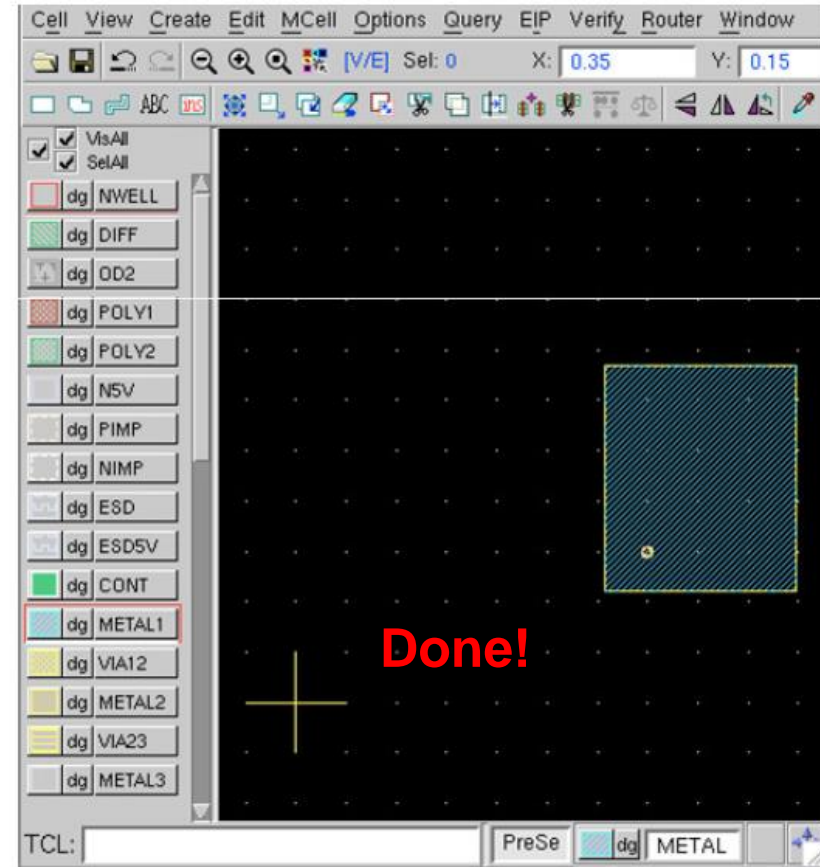
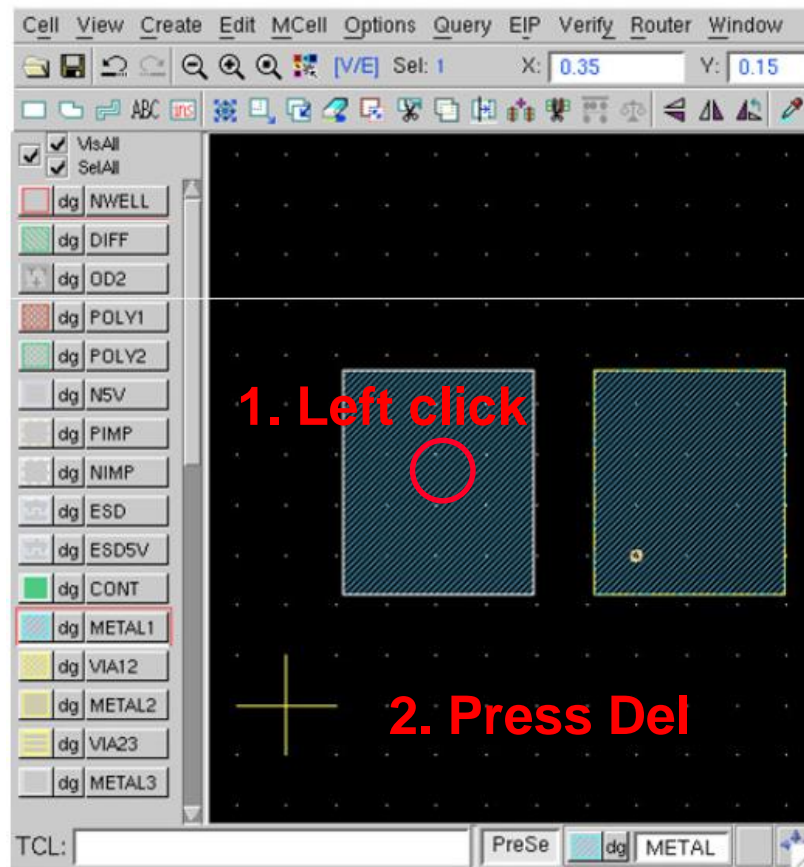
- Press c → select figure → point ref. → point dest.



Laker – (De)lete

❑ Delete (Del)

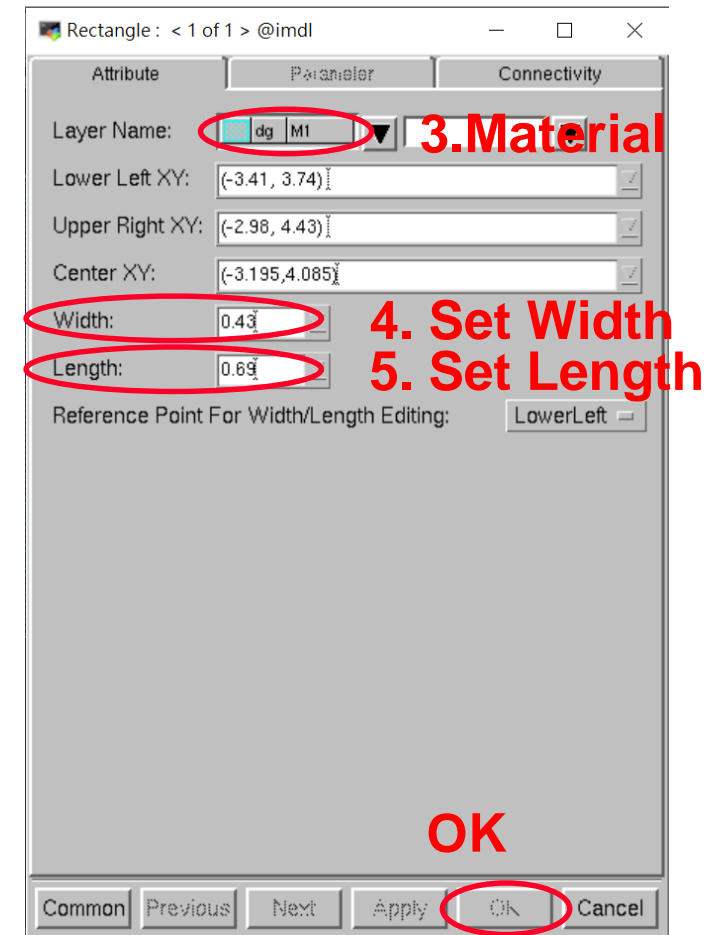
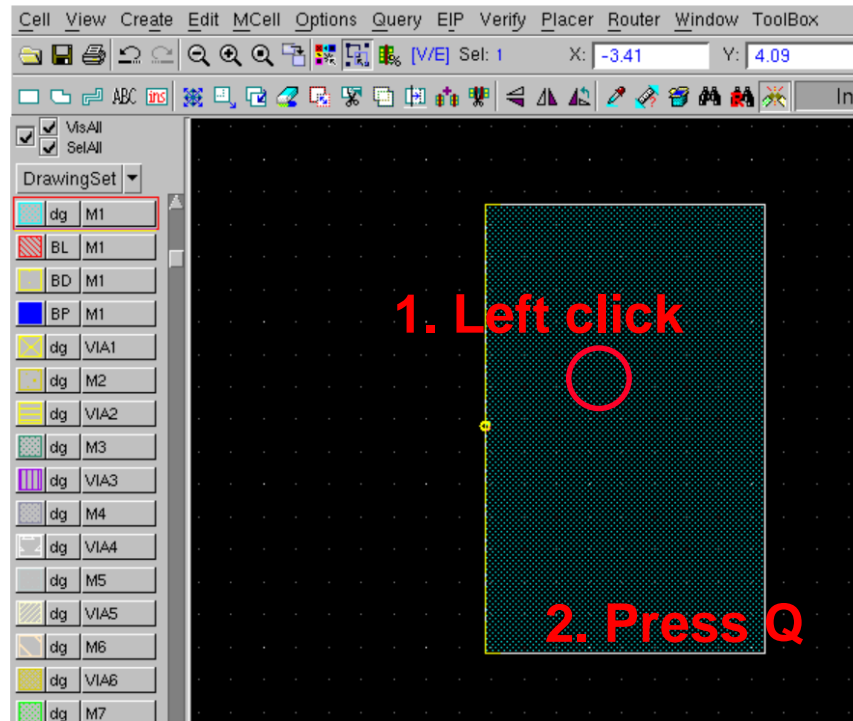
- Select figure → press Del



Laker – (Q)uality

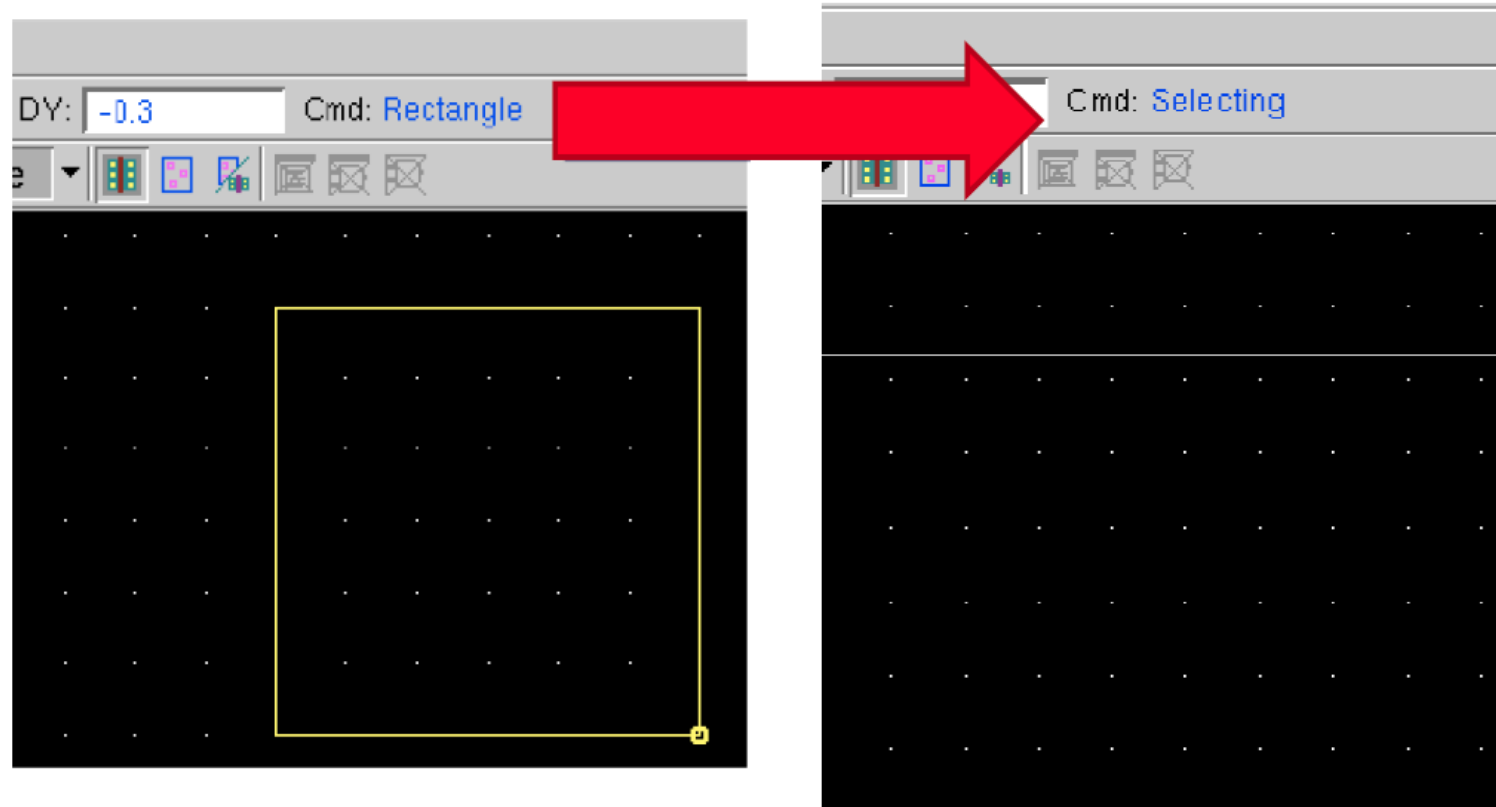
❑ Quality (Q)

- Select figure → press Q → Edit

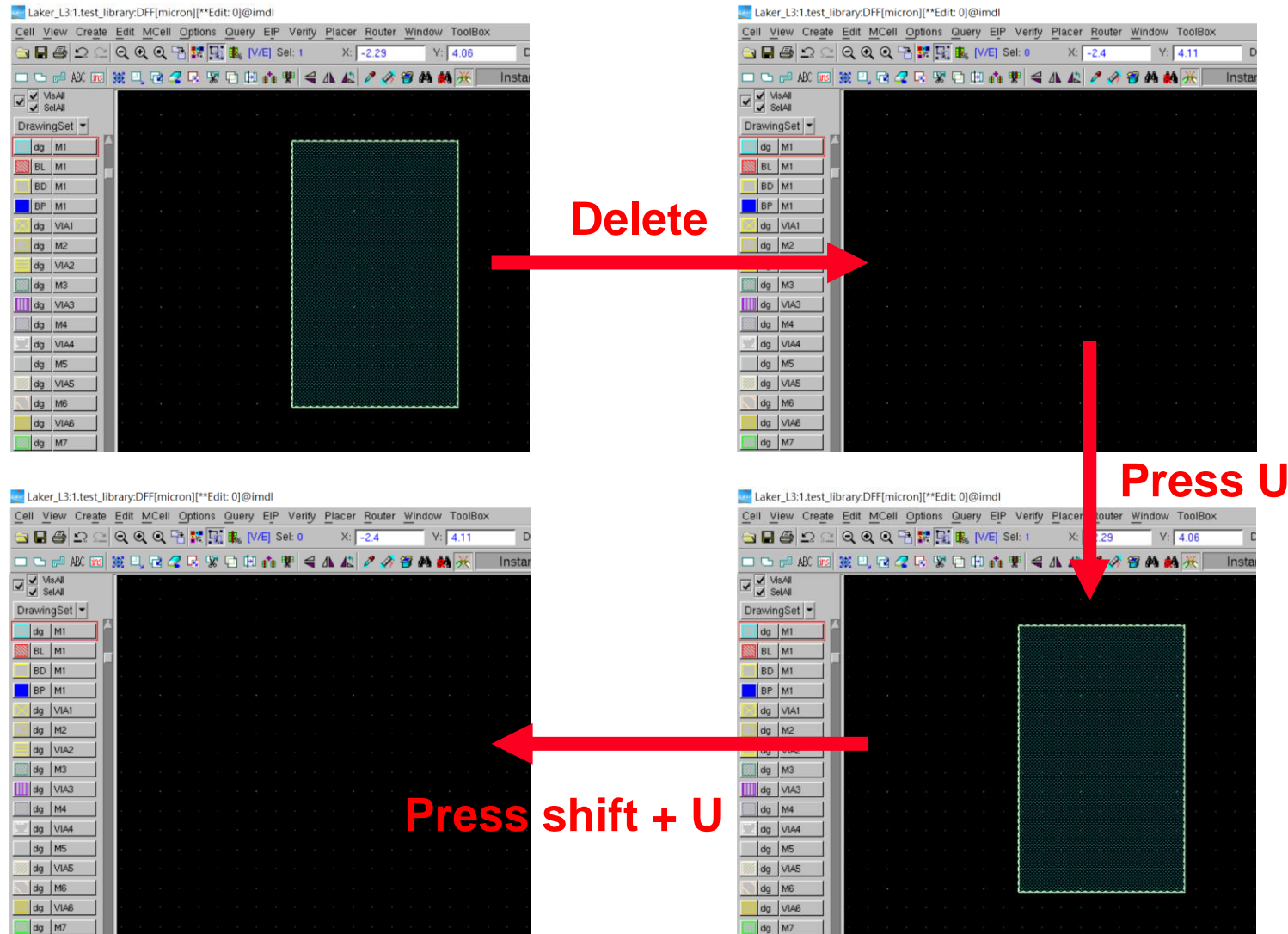


Laker – (Esc)ape

- ❑ Release from Attitude (Esc)
 - Press after every operation (Good habit)



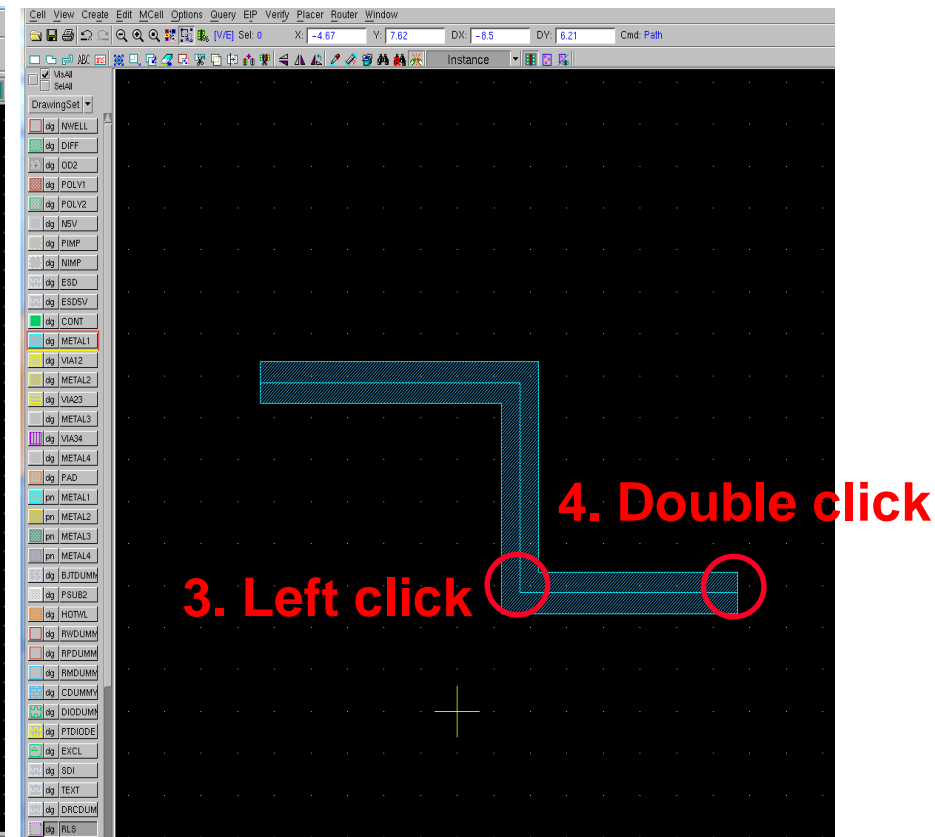
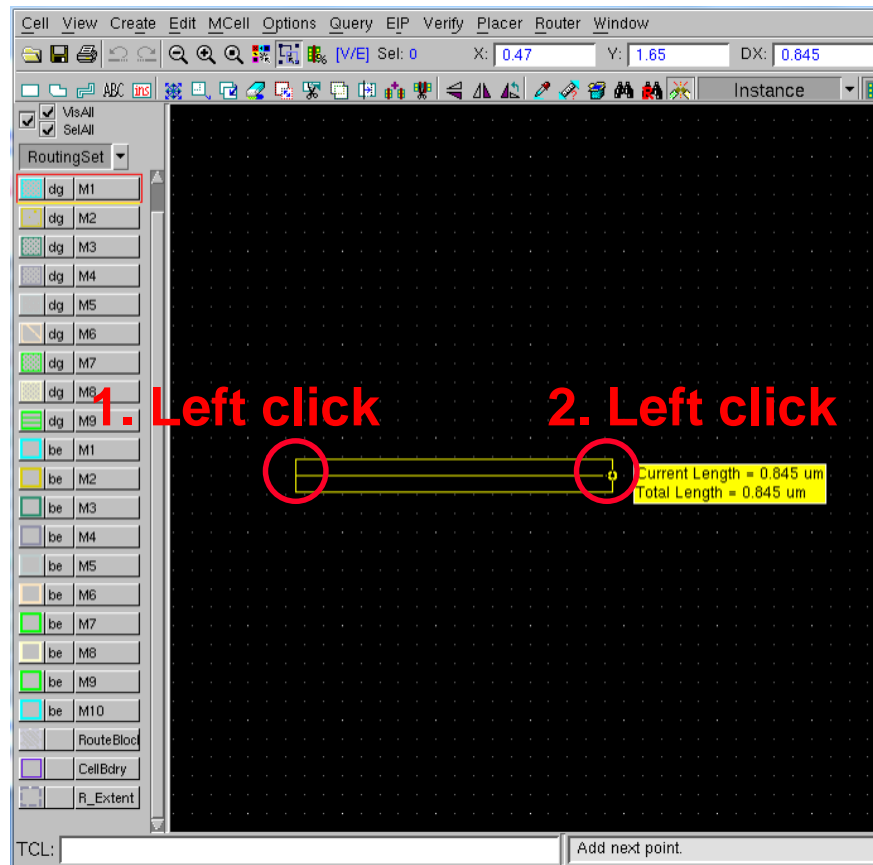
Laker – (U)ndo



Laker – (P)ath

□ Path(p)

- Choose a material → Press p → point to turn → double click to dest.

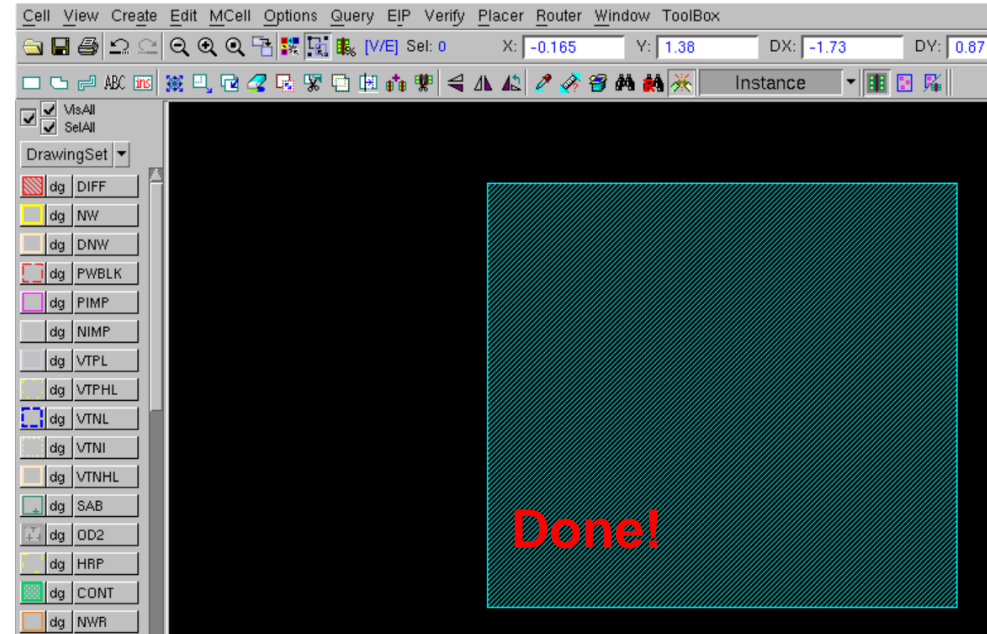
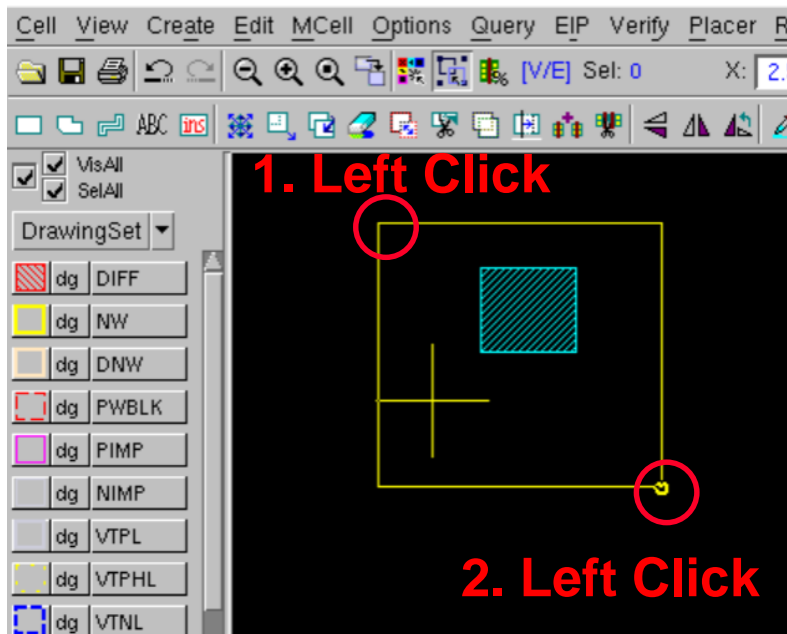


Laker – (Z)oom (1/3)

- ❑ Zoom in (ctrl + z)
- ❑ Zoom out (shift + z)
- ❑ Fit to screen (f)
- ❑ Zoom to area (z + mouse left click)
 - Press z → point ref. → point dest.
- ❑ Zoom to area (mouse right drag)
 - Right click at ref. → drag to dest.

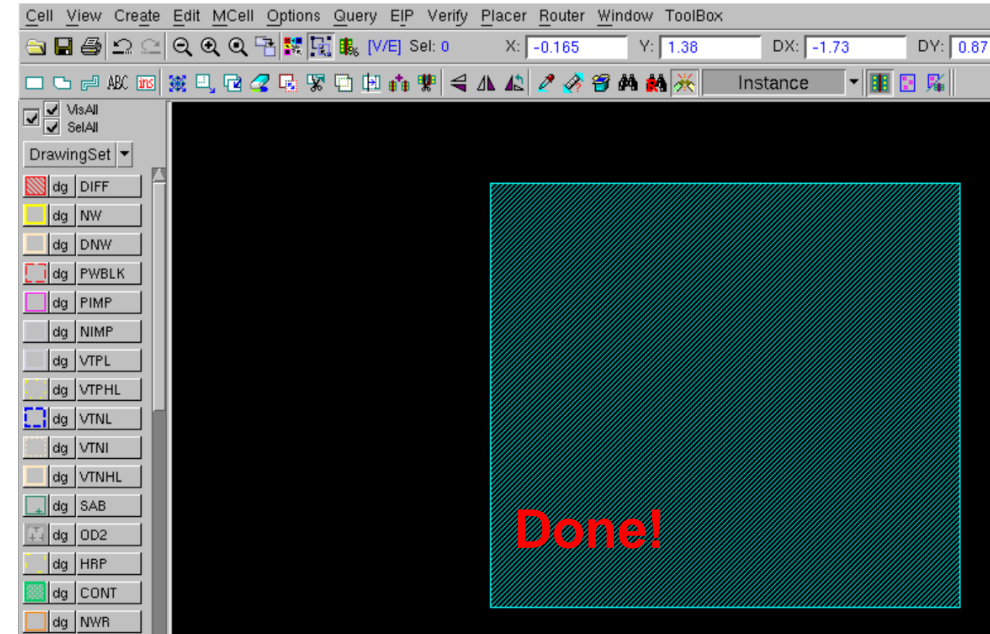
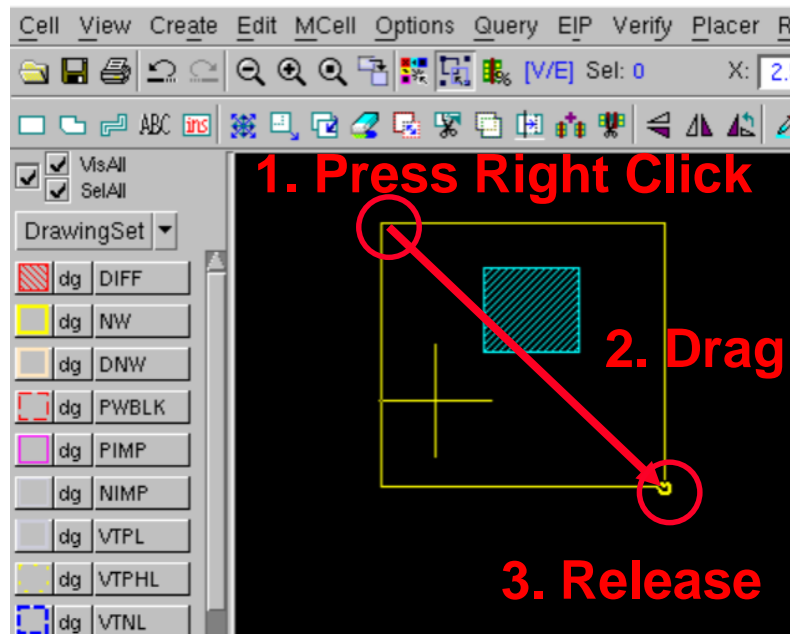
Laker – (Z)oom (2/3)

- ❑ Zoom to area (z + mouse left click)
 - Press z → point ref. → point dest.



Laker – (Z)oom (3/3)

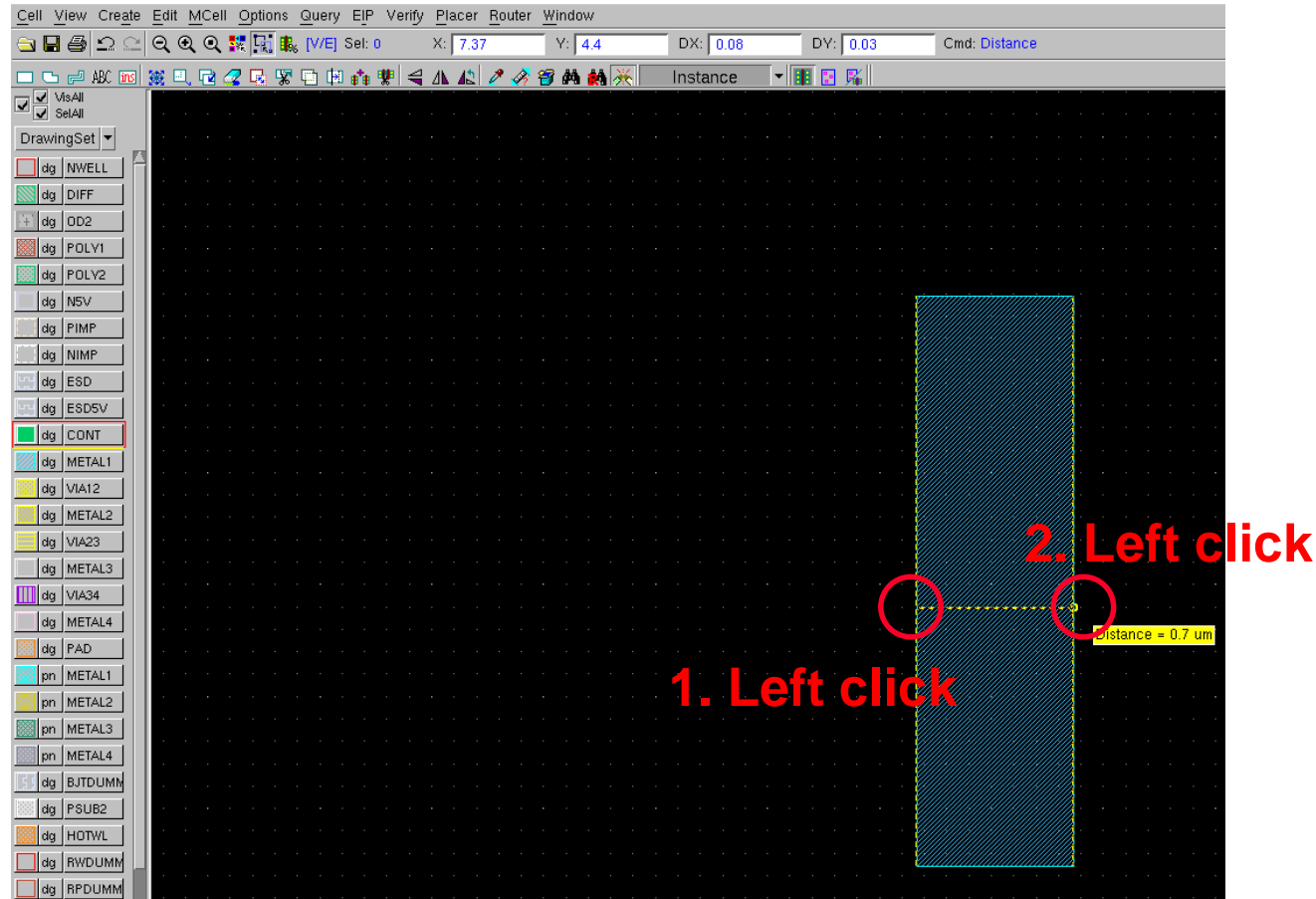
- ❑ Zoom to area (mouse right drag)
 - Right click at ref. → drag to dest.



Laker – (D)istance

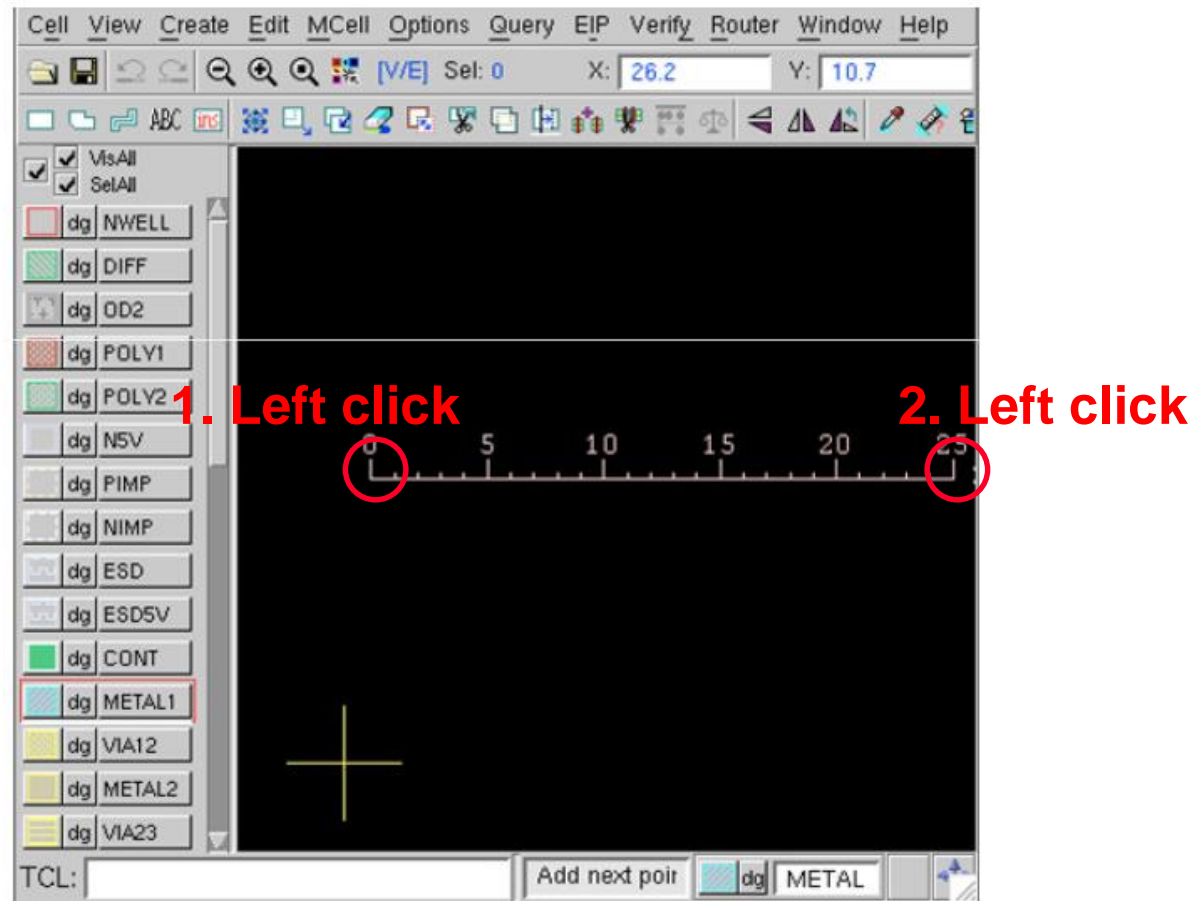
❑ Measure Distance (d)

- Press d → point ref. → stop the mouse at dest.



Laker – Mar(K)er

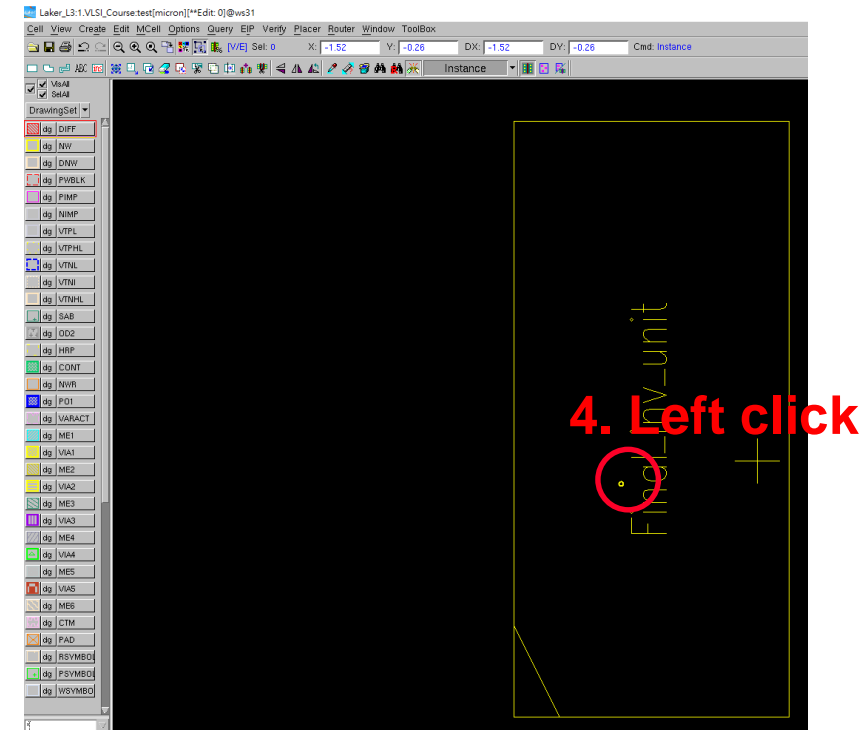
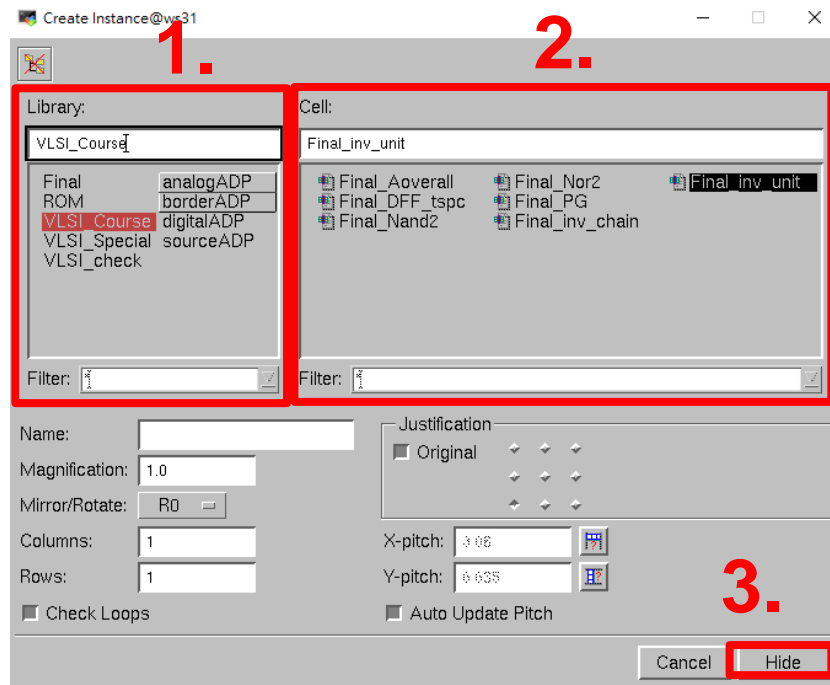
- ❑ Marker (k) /Remove all Markers(shift + k)
 - Press k → point ref. → point dest.



Laker – (I)nstance (1/2)

❑ Call an Instance (I)

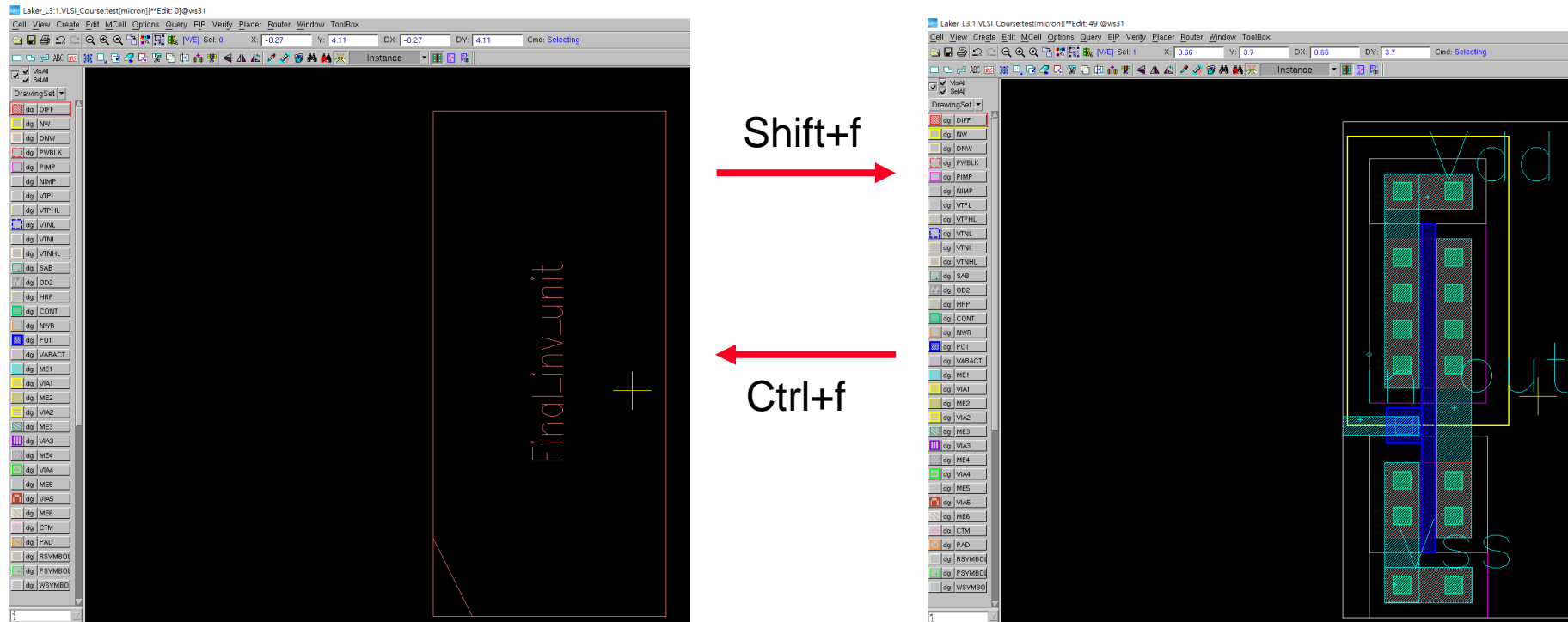
- Press I → select the cell → place the cell



Laker – (I)nstance (2/2)

❑ Min/Max View Level (ctrl/shift+f)

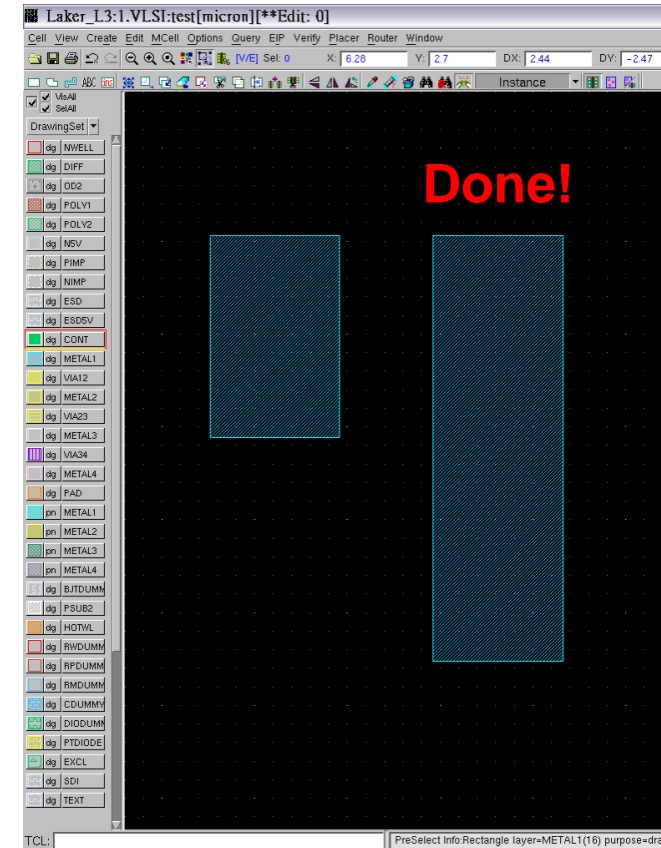
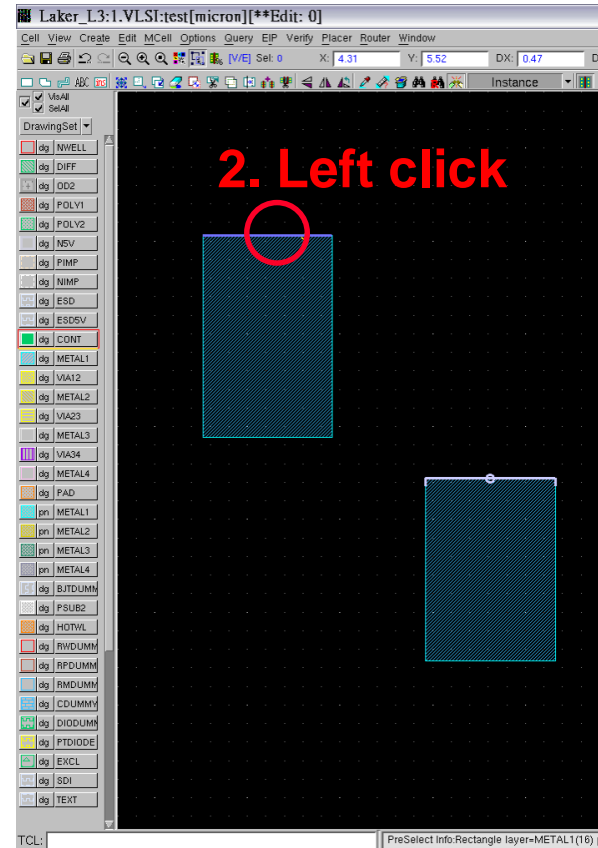
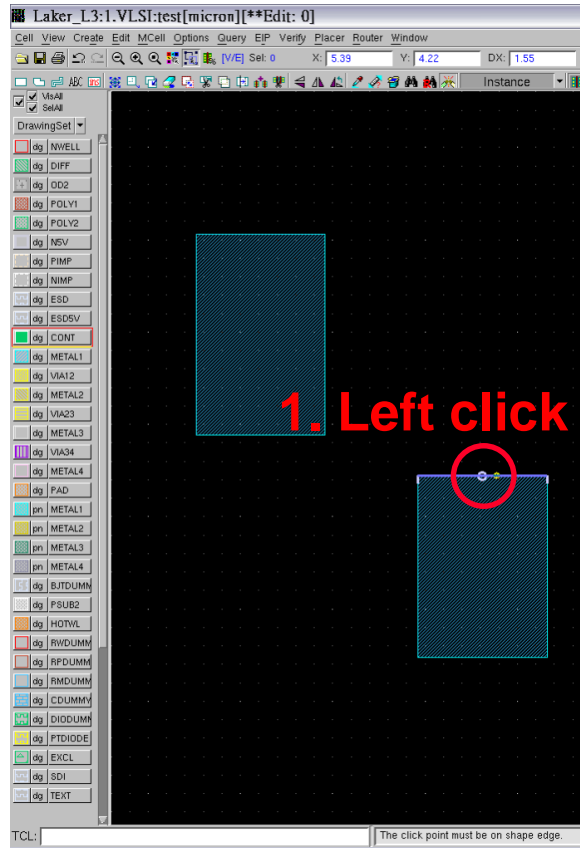
→ After add an instance, we can choose the view level we want.



Laker – (A)lign

□ Align (a)

- Press a → point ref. → point dest.



Practice – Align (Part A)

- ❑ Part A: Please try the Align function with different ref. and dest. position, and write down the results :

Reference point	Destination point
1. Middle point of edge 2. Vertex	1. Middle point of edge 2. Edge 3. Vertex

Practice – Align (Part B)

- ❑ Part B: Please try the Align function with **only select the edge**, and repeat part A.

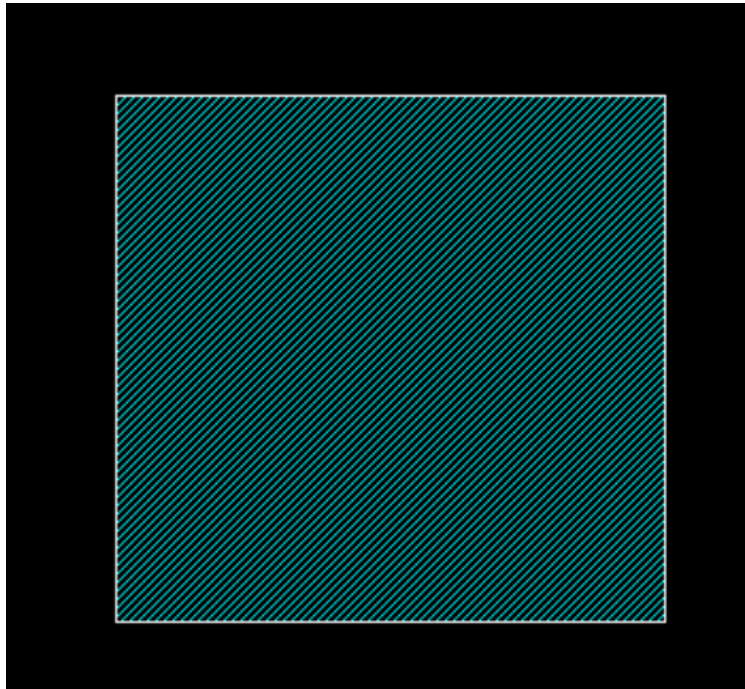


Fig1. Select the whole block

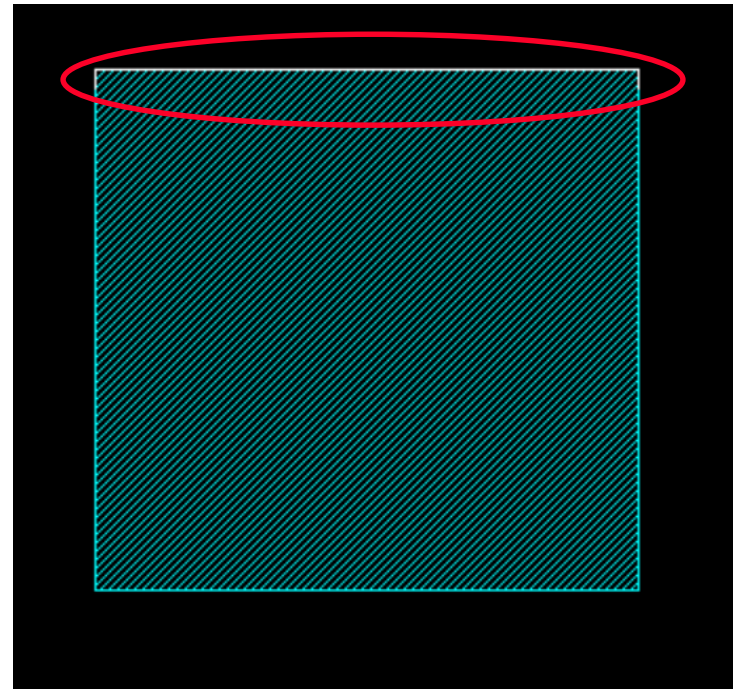
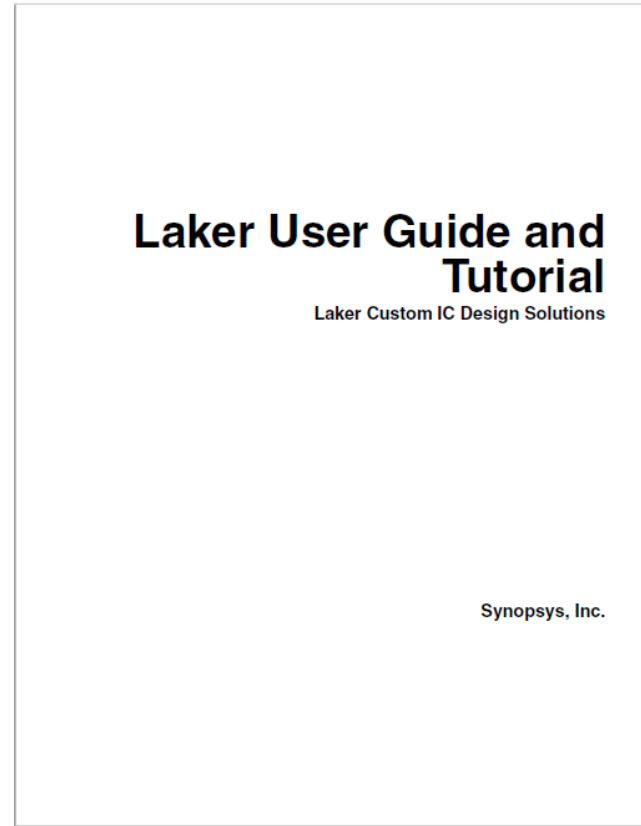


Fig2. Only select the edge

Advanced hot key

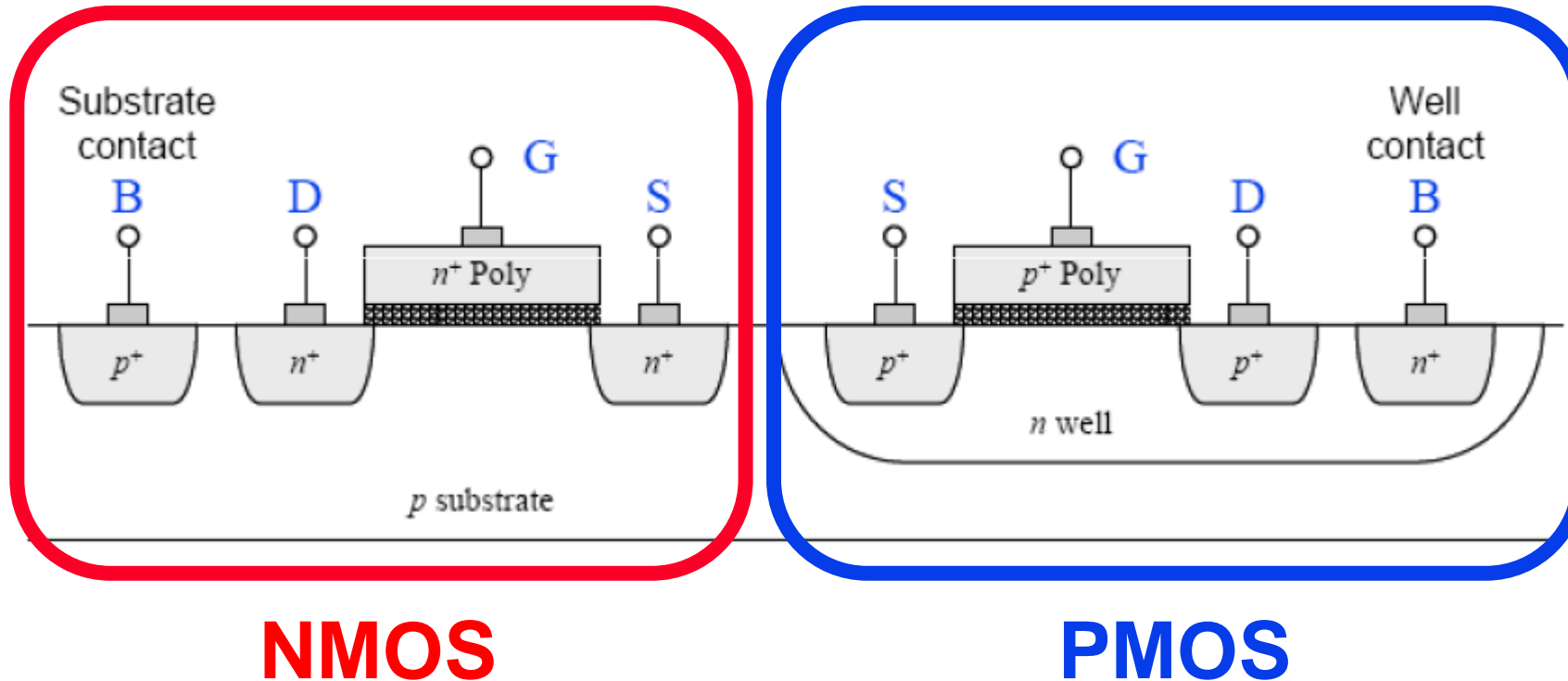
- ❑ If you want to learn more advanced hot key or get more detailed information, please refer to Laker User Guide and Tutorial.



Process & Layout

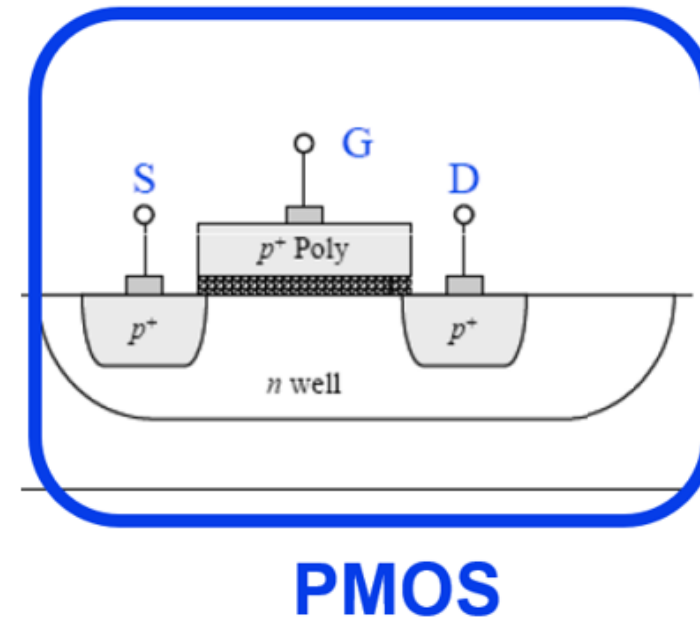
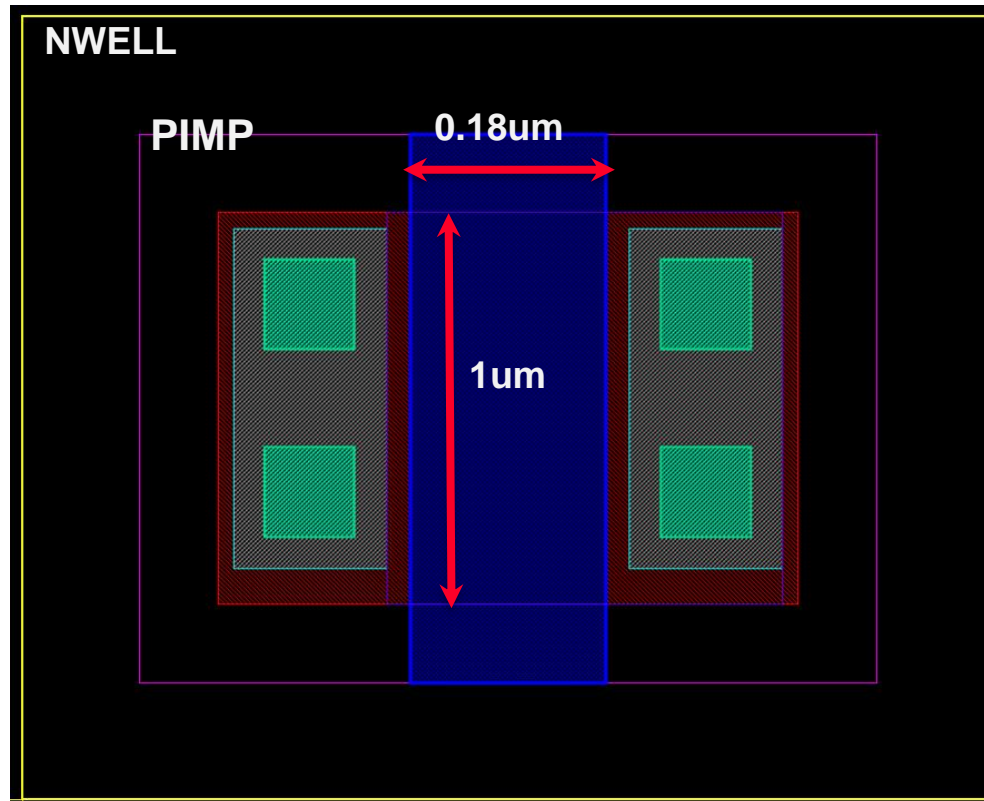
Process

❑ Cross Section View of NMOS & PMOS



Example – PMOS

- Draw a PMOS with $L=0.18\mu\text{m}$ $W=1\mu\text{m}$

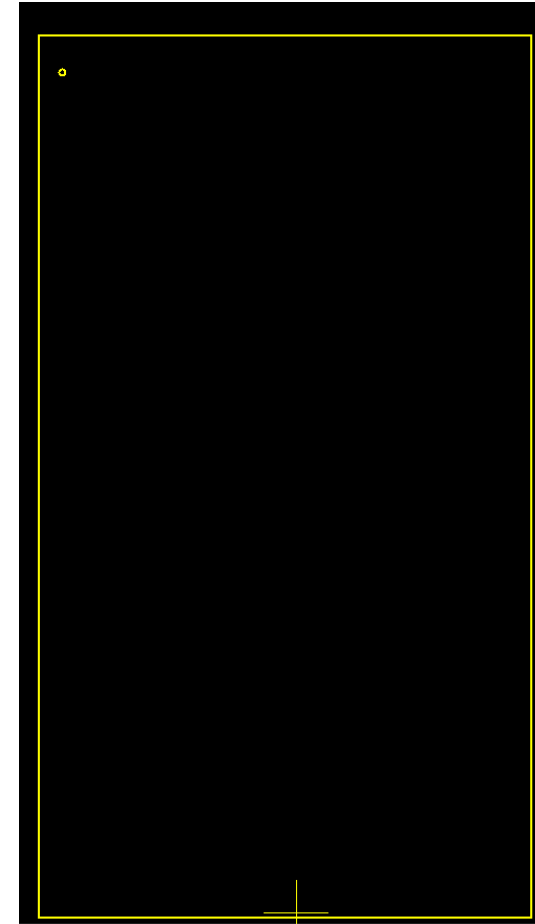
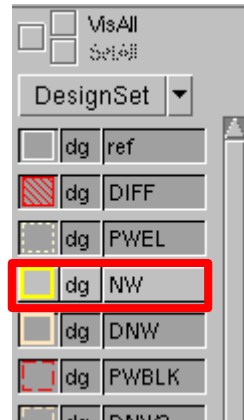
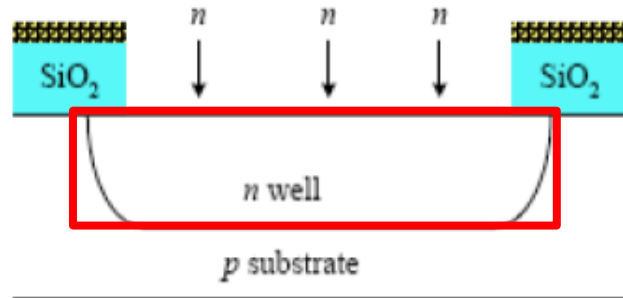


PMOS Process vs. Layout

❑ Process v.s. Layout

- NWELL

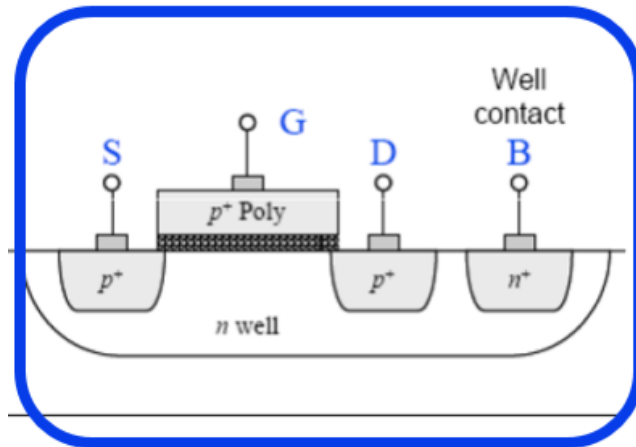
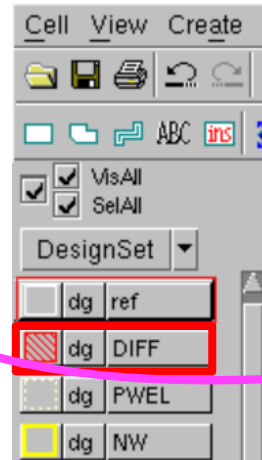
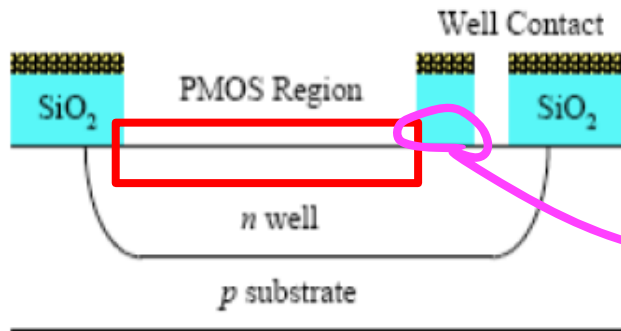
1. N well



PMOS Process vs. Layout

□ Process v.s. Layout

2. Diffusion

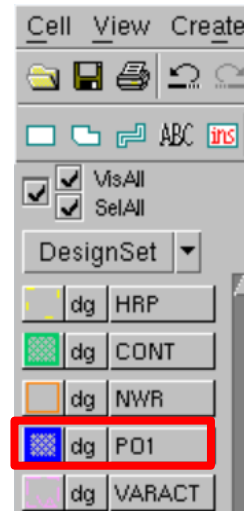
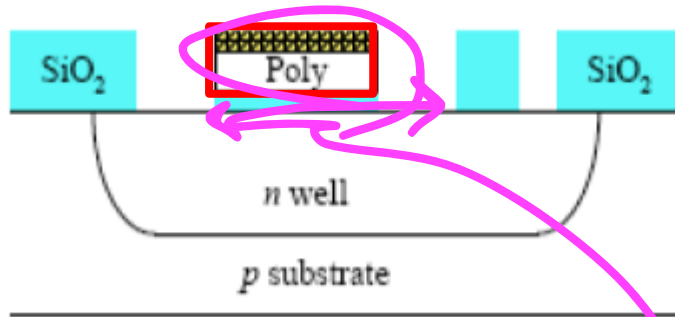


• DIFF

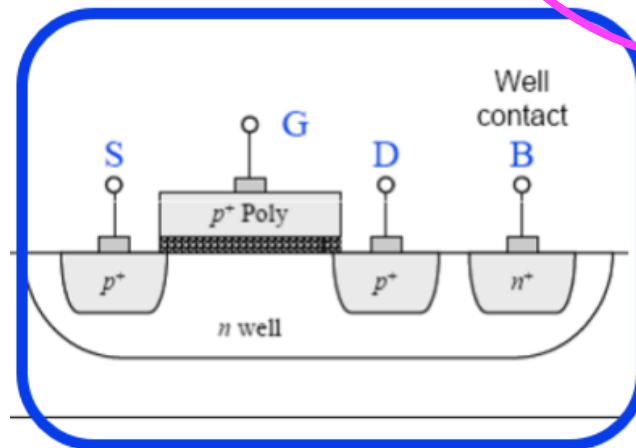
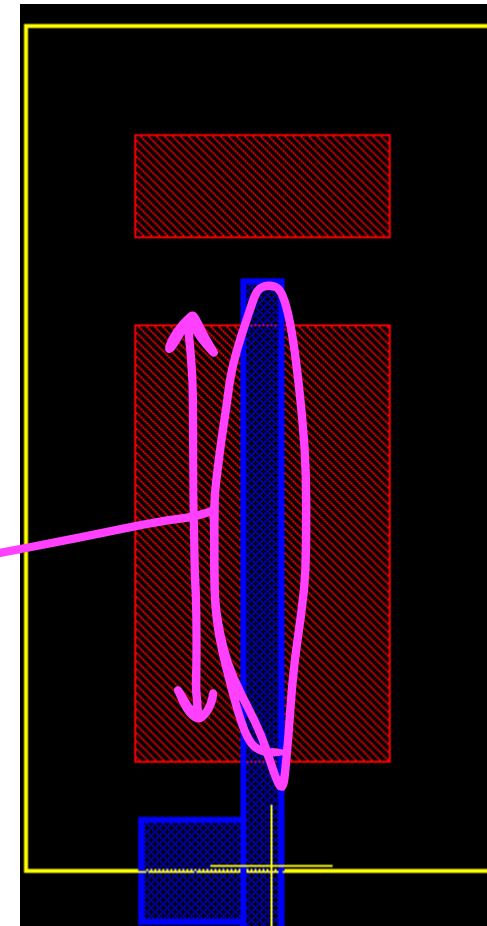


PMOS Process vs. Layout

3. Poly gate

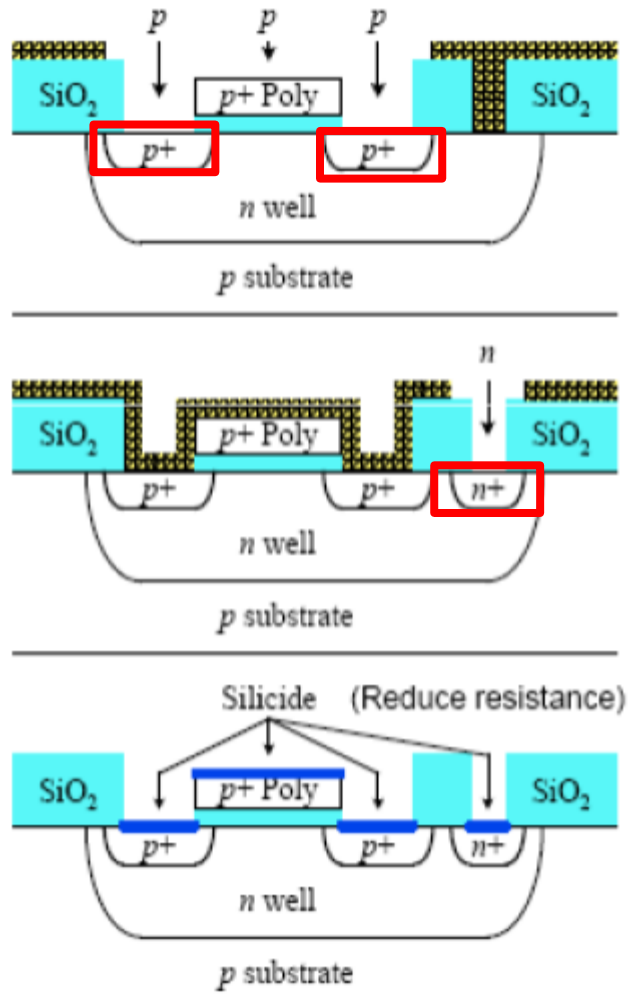


• PO1

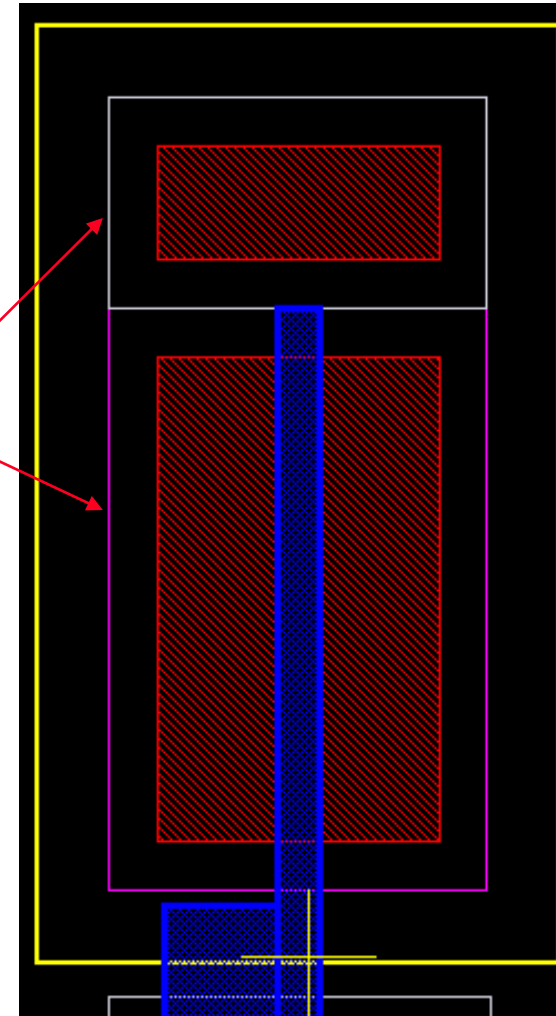
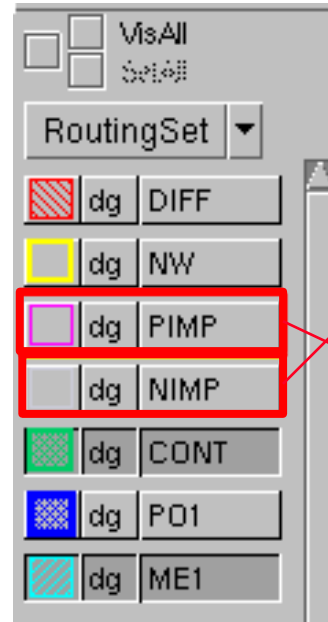


PMOS Process vs. Layout

4. P+/N+ Implant

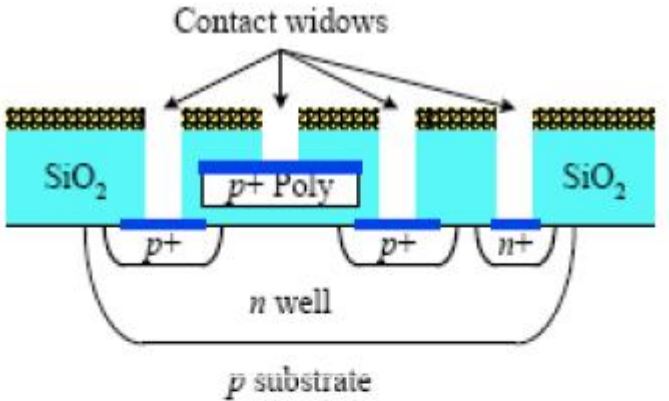


• PIMP



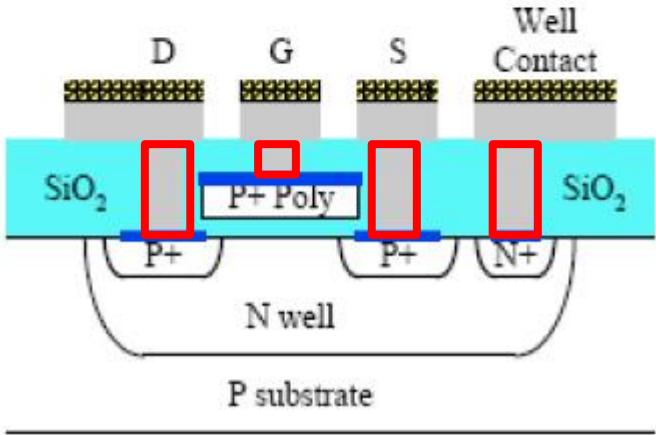
PMOS Process vs. Layout

5. Contacts

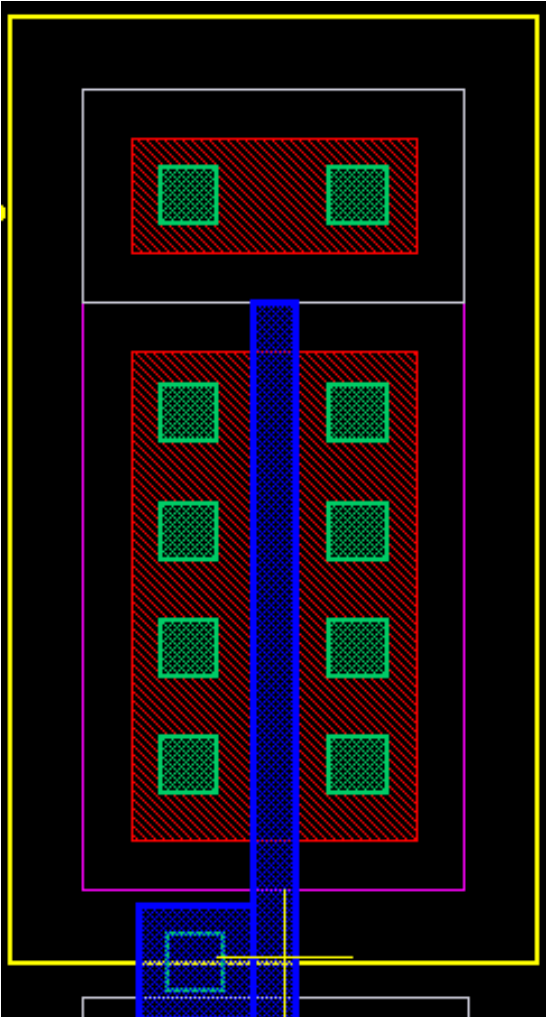


	dg	POLY2
	dg	N5V
	dg	PIMP
	dg	NIMP
	dg	ESD
	dg	ESD5V
	dg	CONT
	dg	METAL1
	dg	VIA12

↓ Metal: Al or Cu

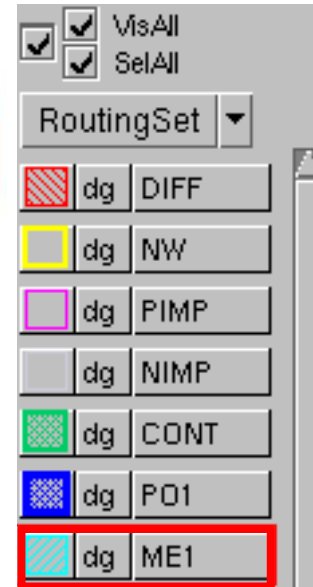
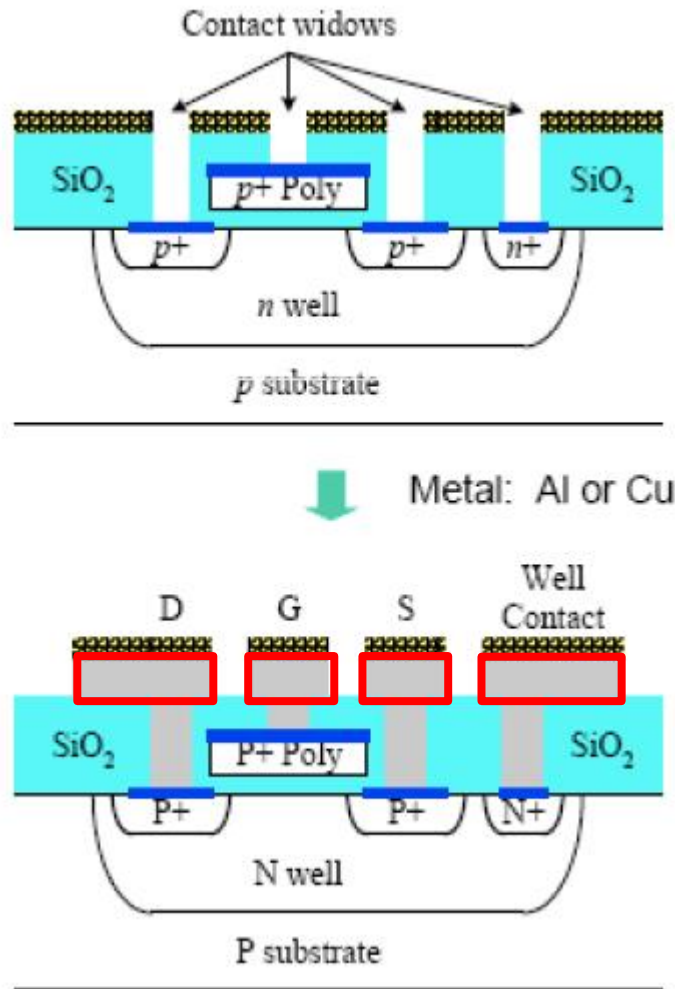


• CONT

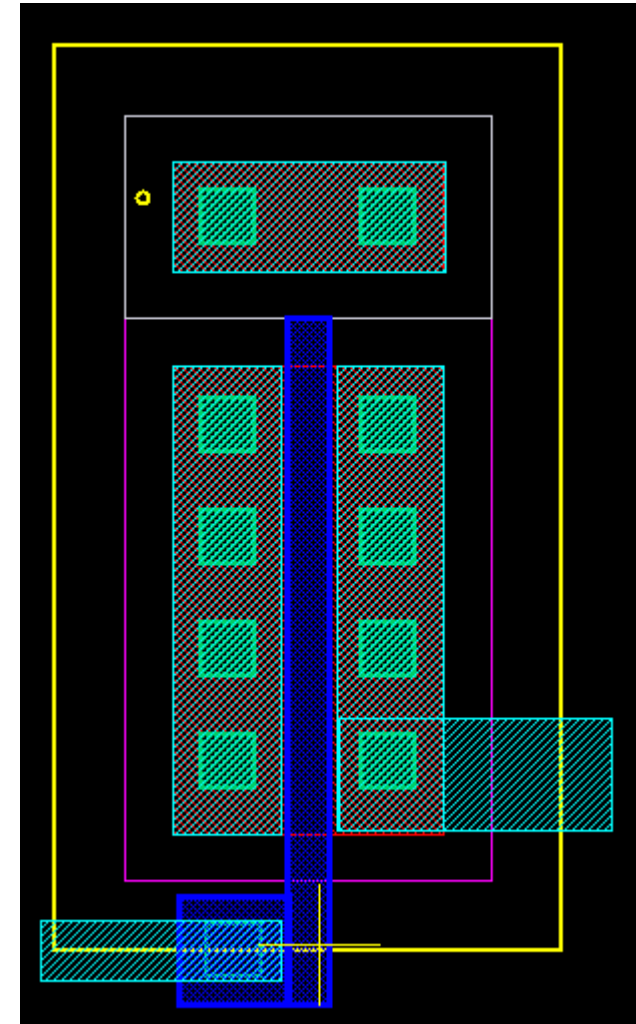


PMOS Process vs. Layout

5. Metal lines

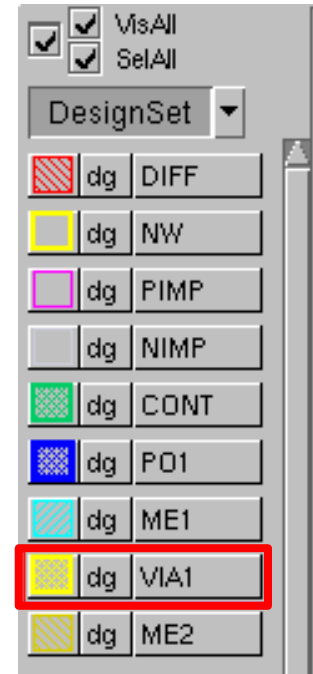
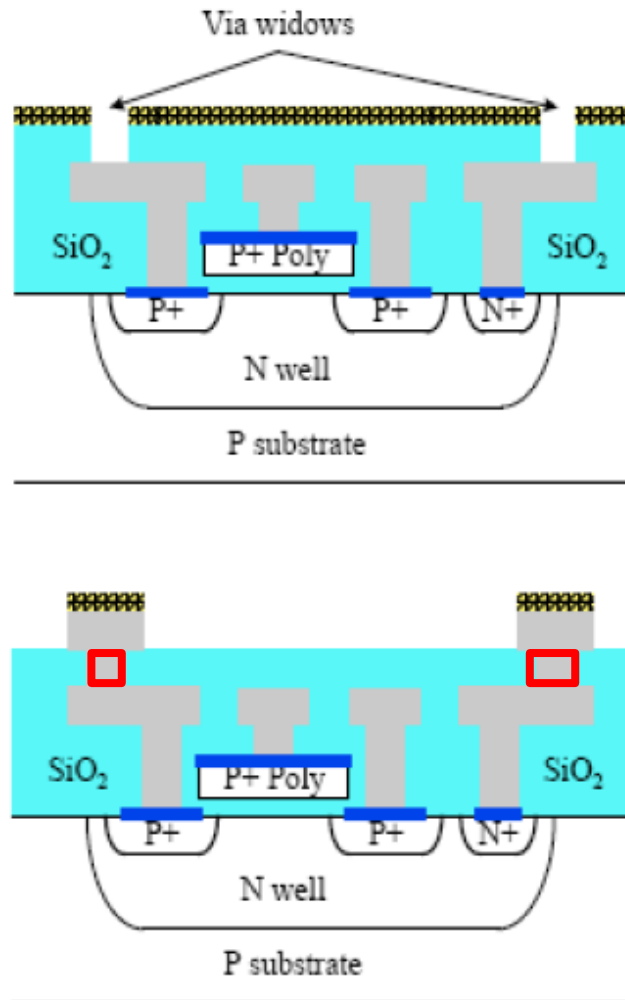


• ME1

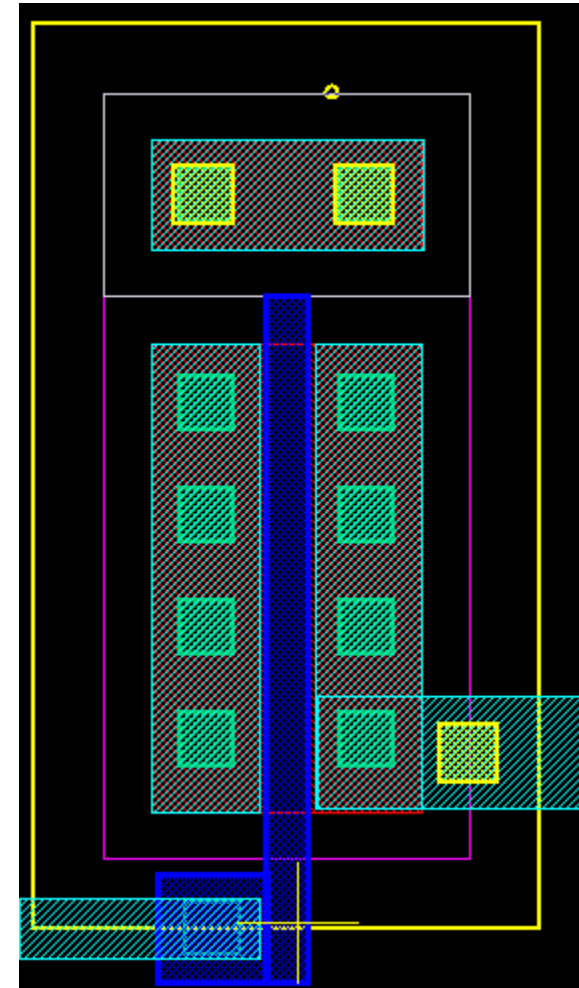


PMOS Process vs. Layout

6. Metal vias/lines

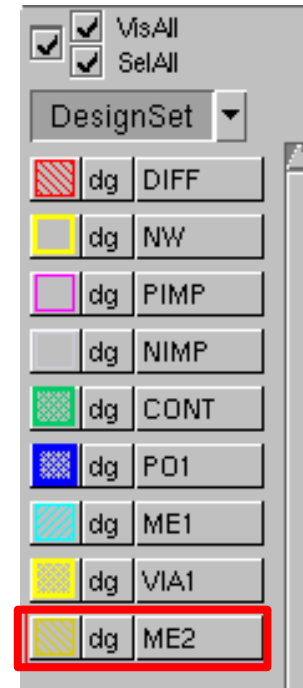
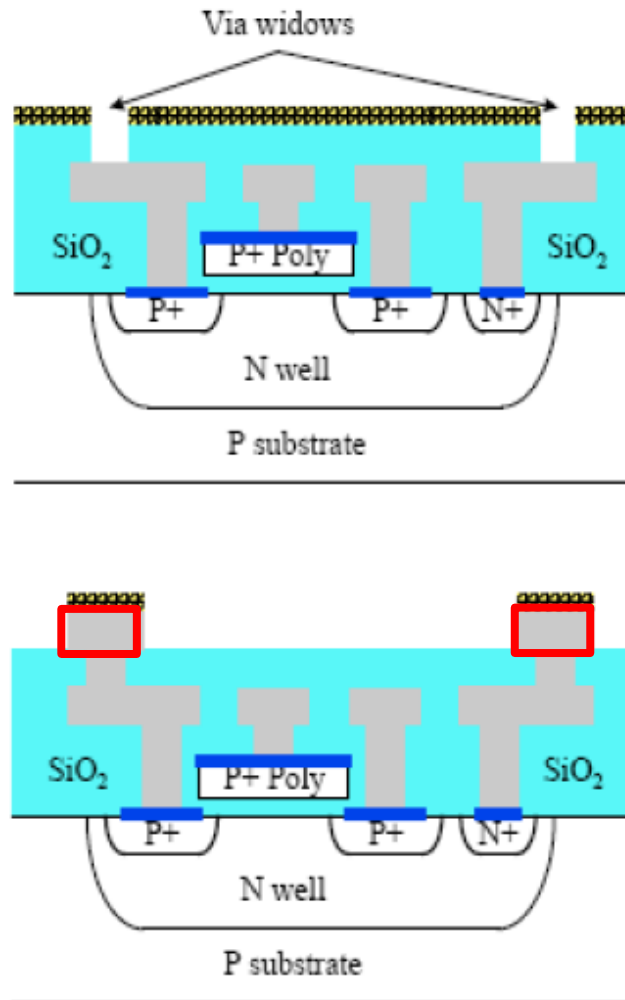


• VIA1

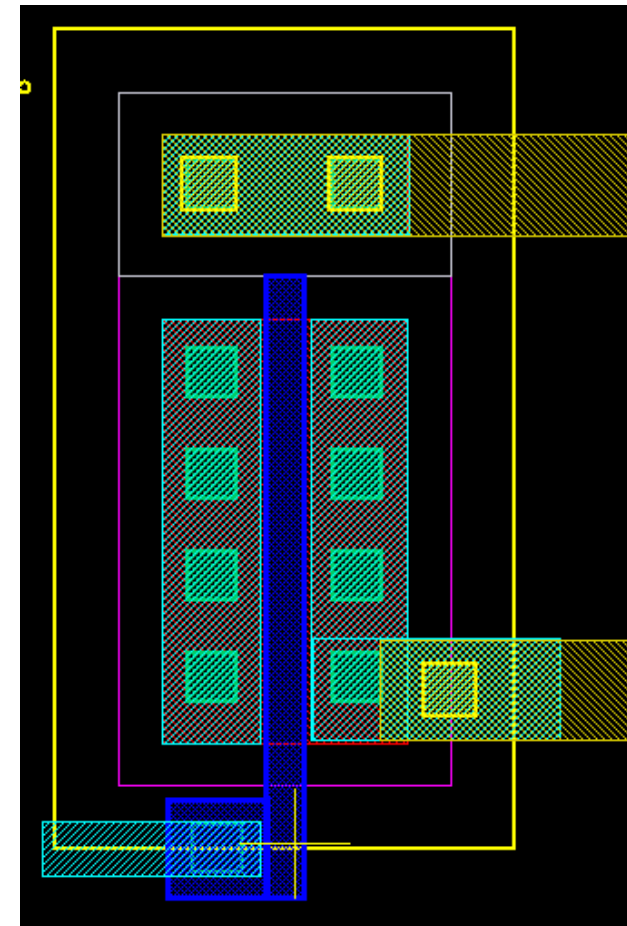


PMOS Process vs. Layout

6. Metal vias/lines



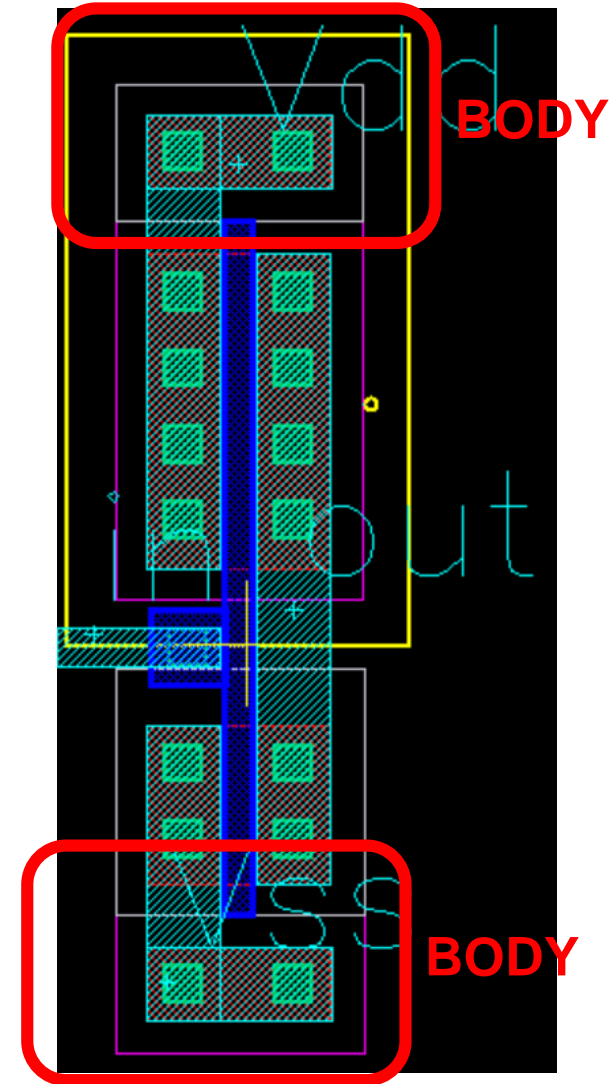
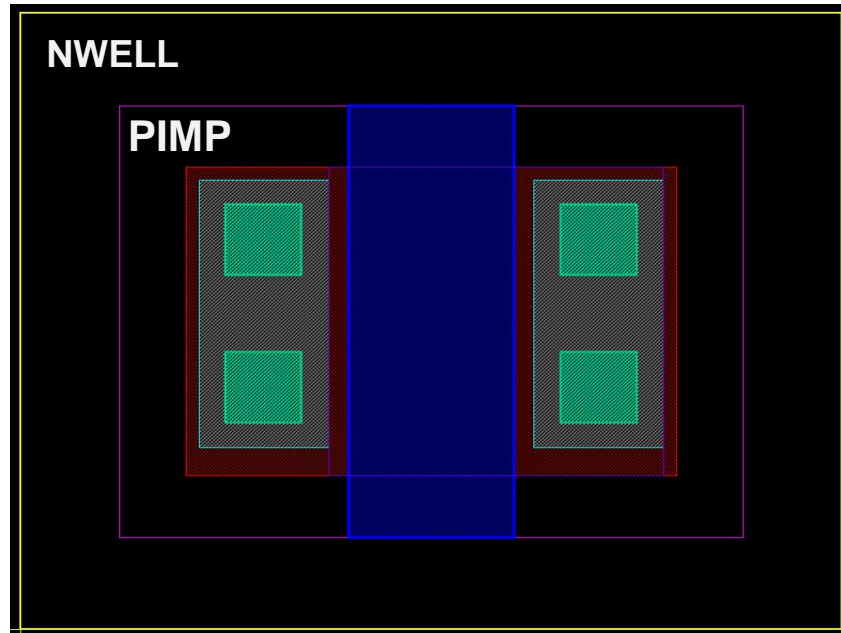
• METAL2



Practice – Inverter

□ Please Draw an Inverter with

- ($W_n/L_n = 1\mu\text{m}/0.18\mu\text{m}$)
- ($W_p/L_p = 2\mu\text{m}/0.18\mu\text{m}$)



Multiply the Width

Multiply the Width

❑ If we have a MOS with multiple of unit sizes, it's impractical to draw it directly. We can use the following 2 method to make it easily to implement.

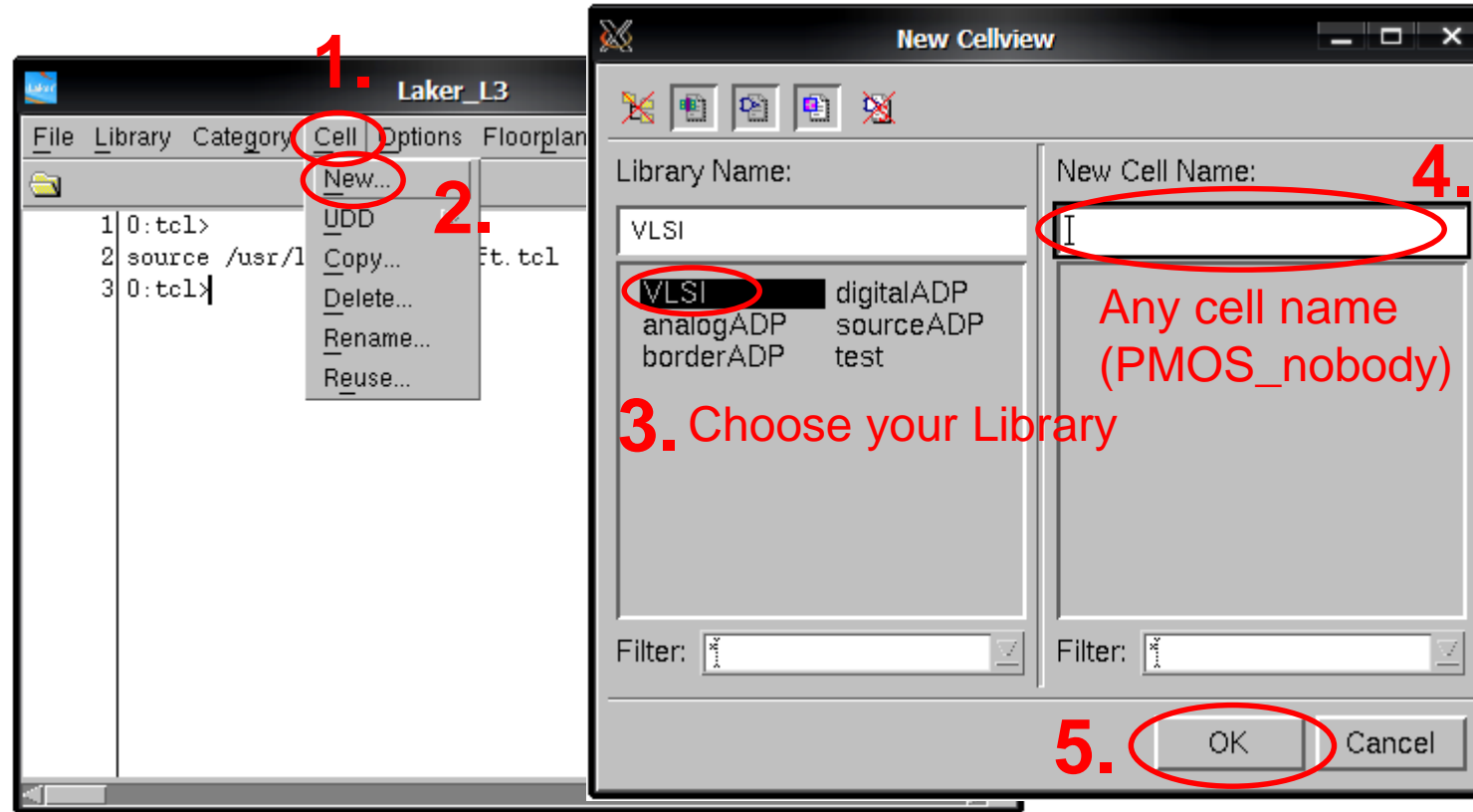
1. Connect with Cell Boundary
2. Fold the MOS

❑ EX: MM1 VD VG VDD VDD p_18 W=2u L=0.18u **m=2**

If we encounter this condition, we can apply the above 2 methods or just draw a MOS with Width=4u Length=0.18u.

Connect with Cell Boundary (1/6)

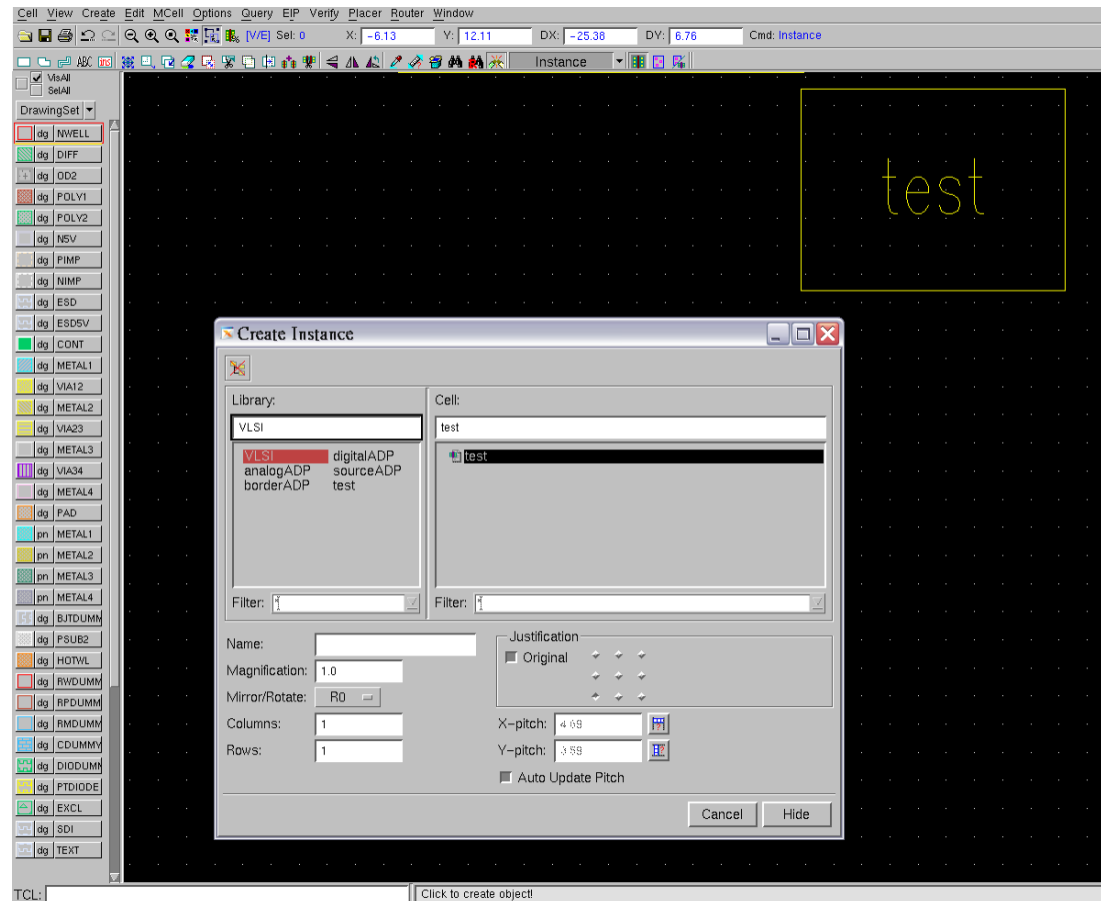
❑ New Cell



Connect with Cell Boundary (2/6)

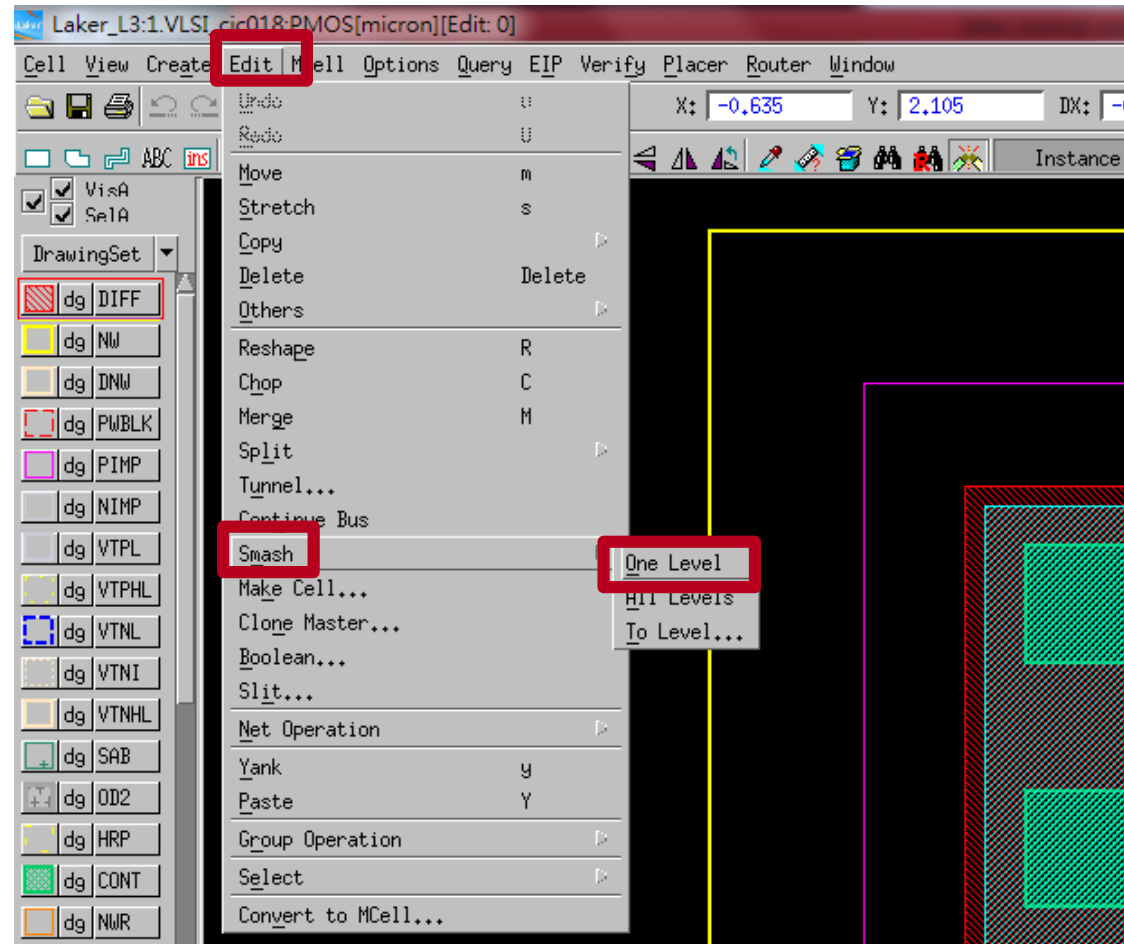
❑ Add Instance (i)

- Press i → choose the instance → press Hide → point dest.



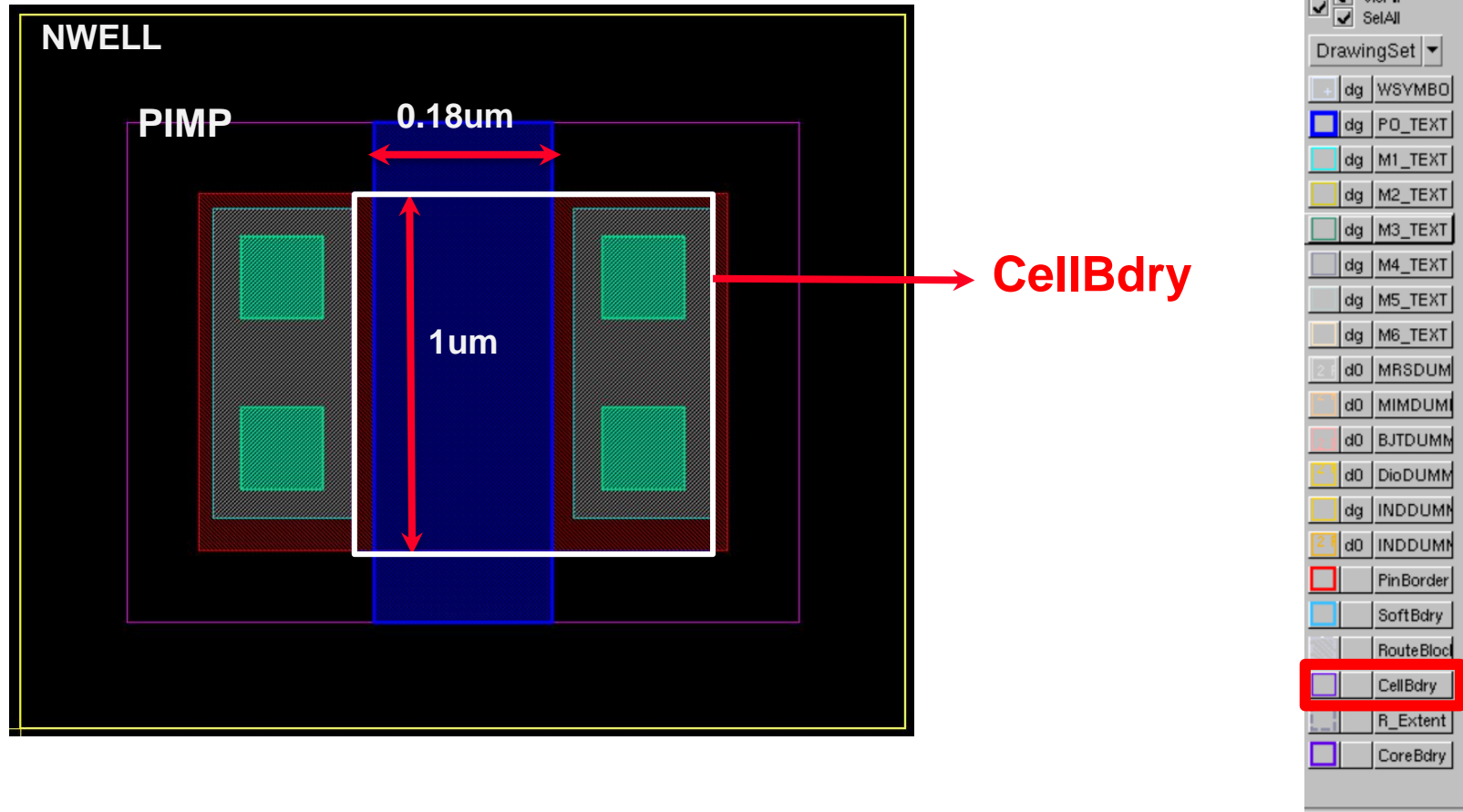
Connect with Cell Boundary (3/6)

❑ Smash



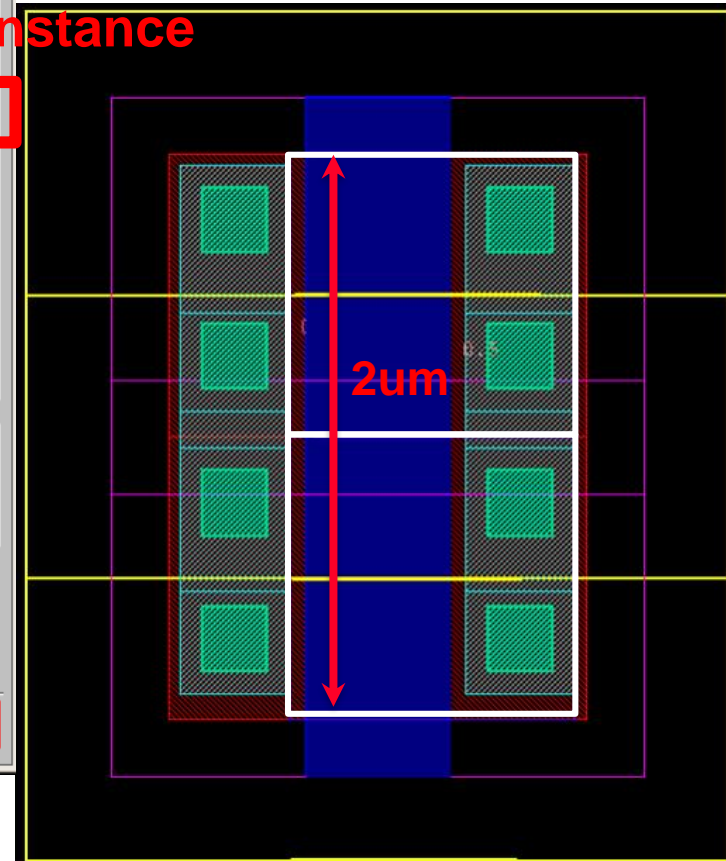
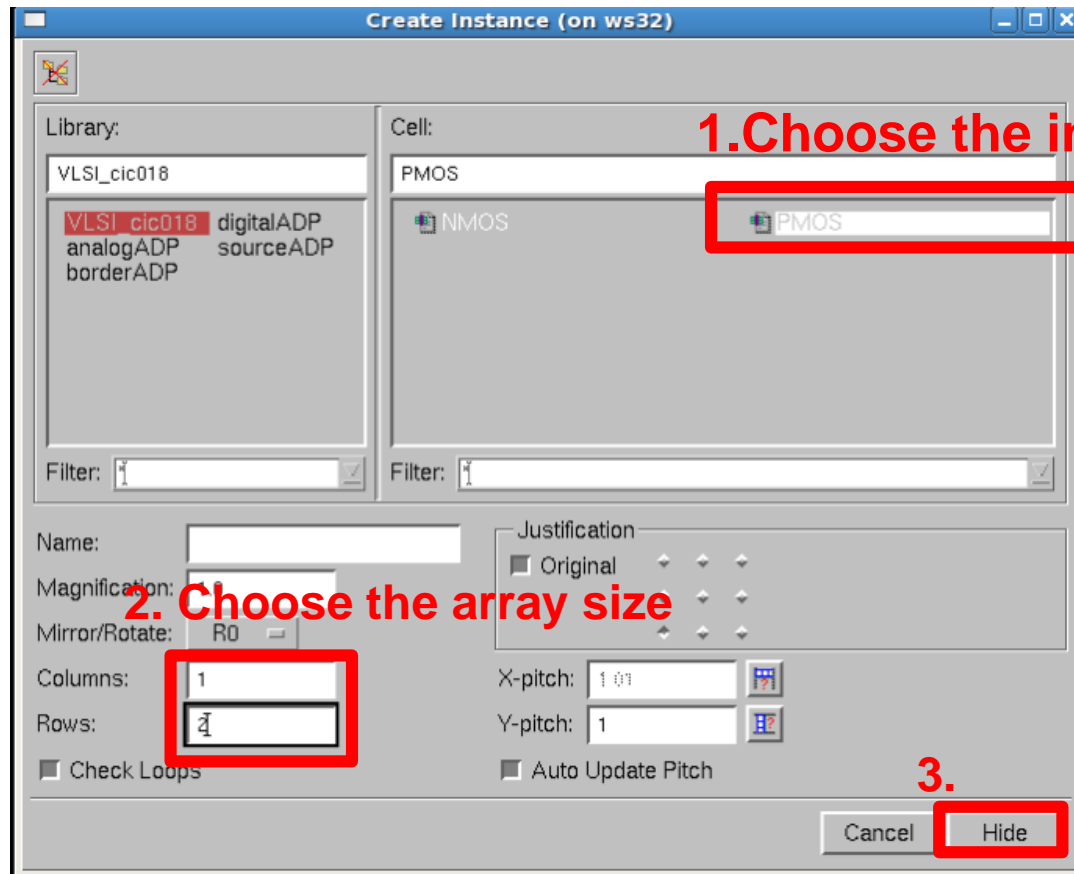
Connect with Cell Boundary (4/6)

- ❑ Add the cell boundary



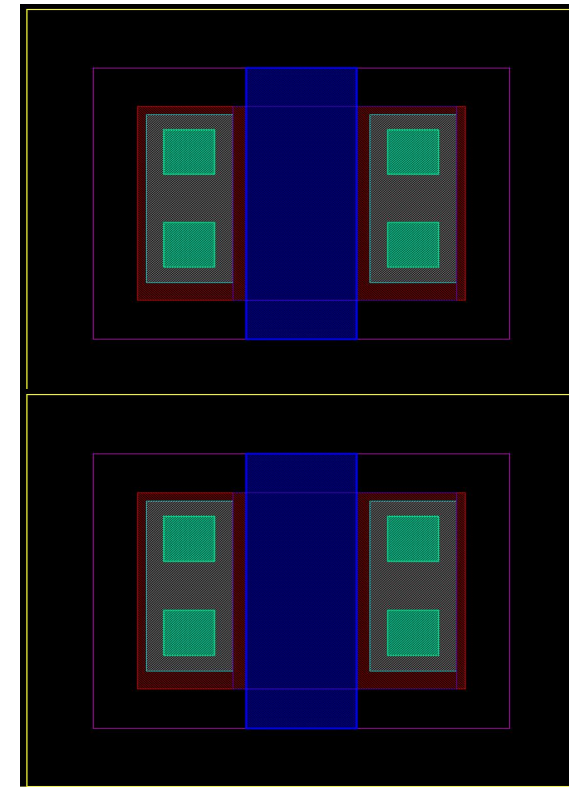
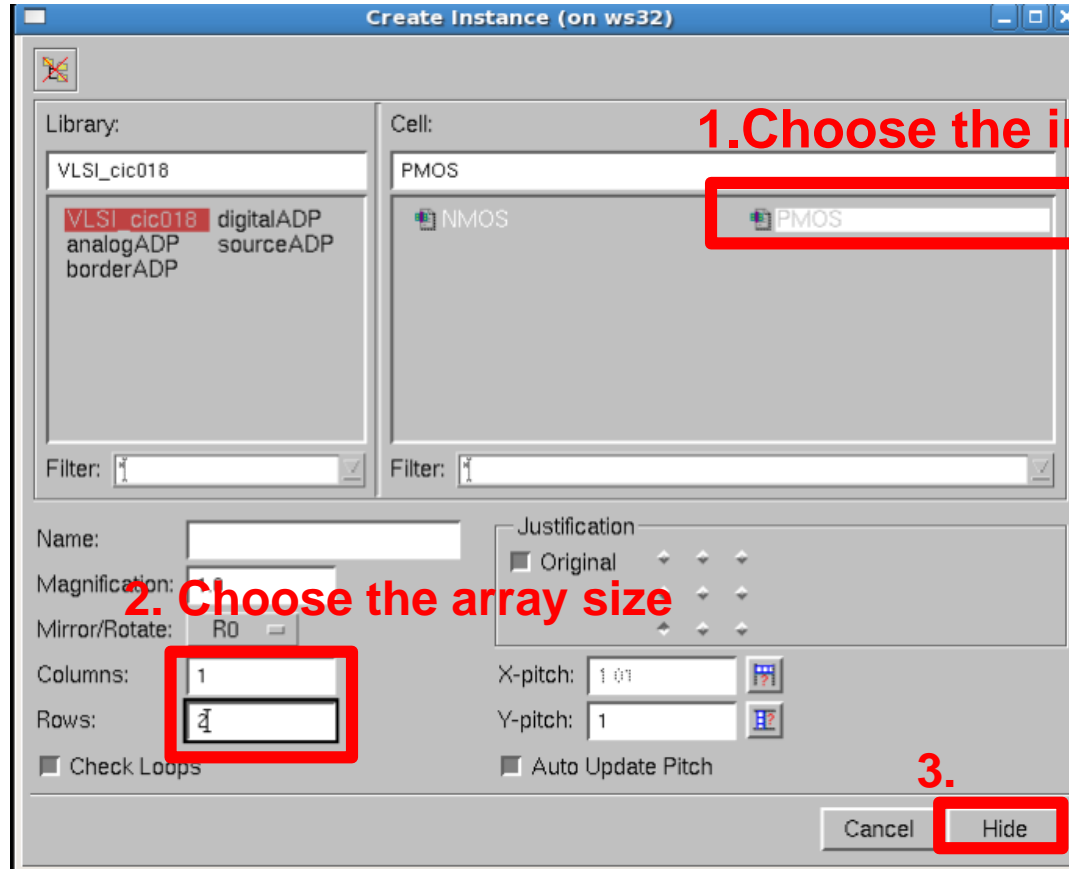
Connect with Cell Boundary (5/6)

❑ Add Instance (i)



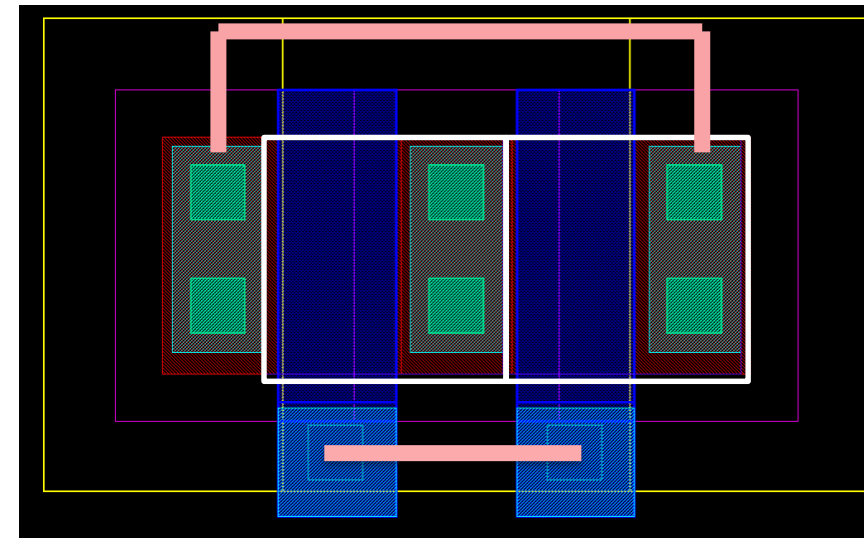
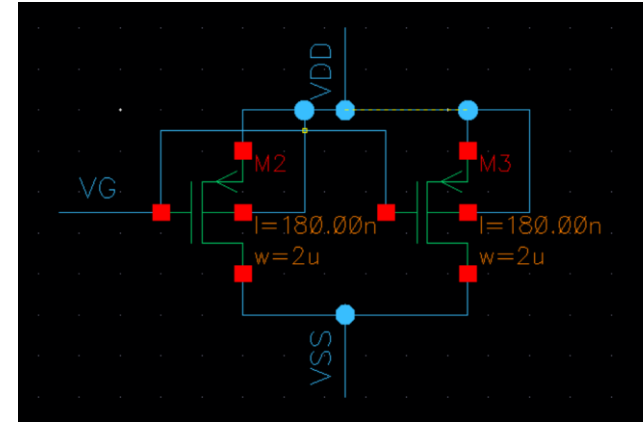
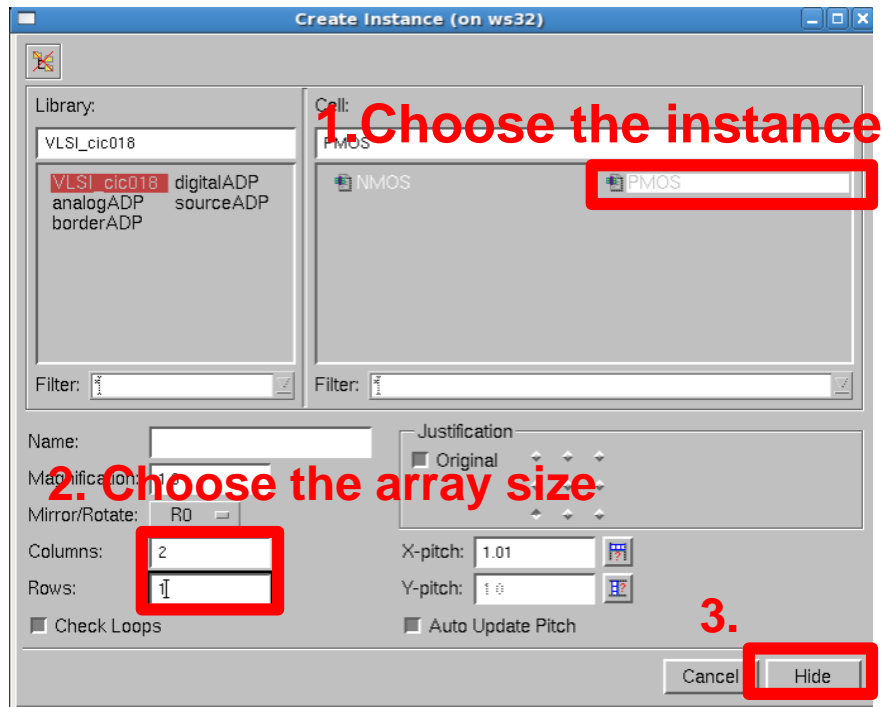
Connect with Cell Boundary (6/6)

- ❑ Fail case : If without the Cell Boundary...



Folded MOS

- ❑ Another way to multiple the width, folded MOS.

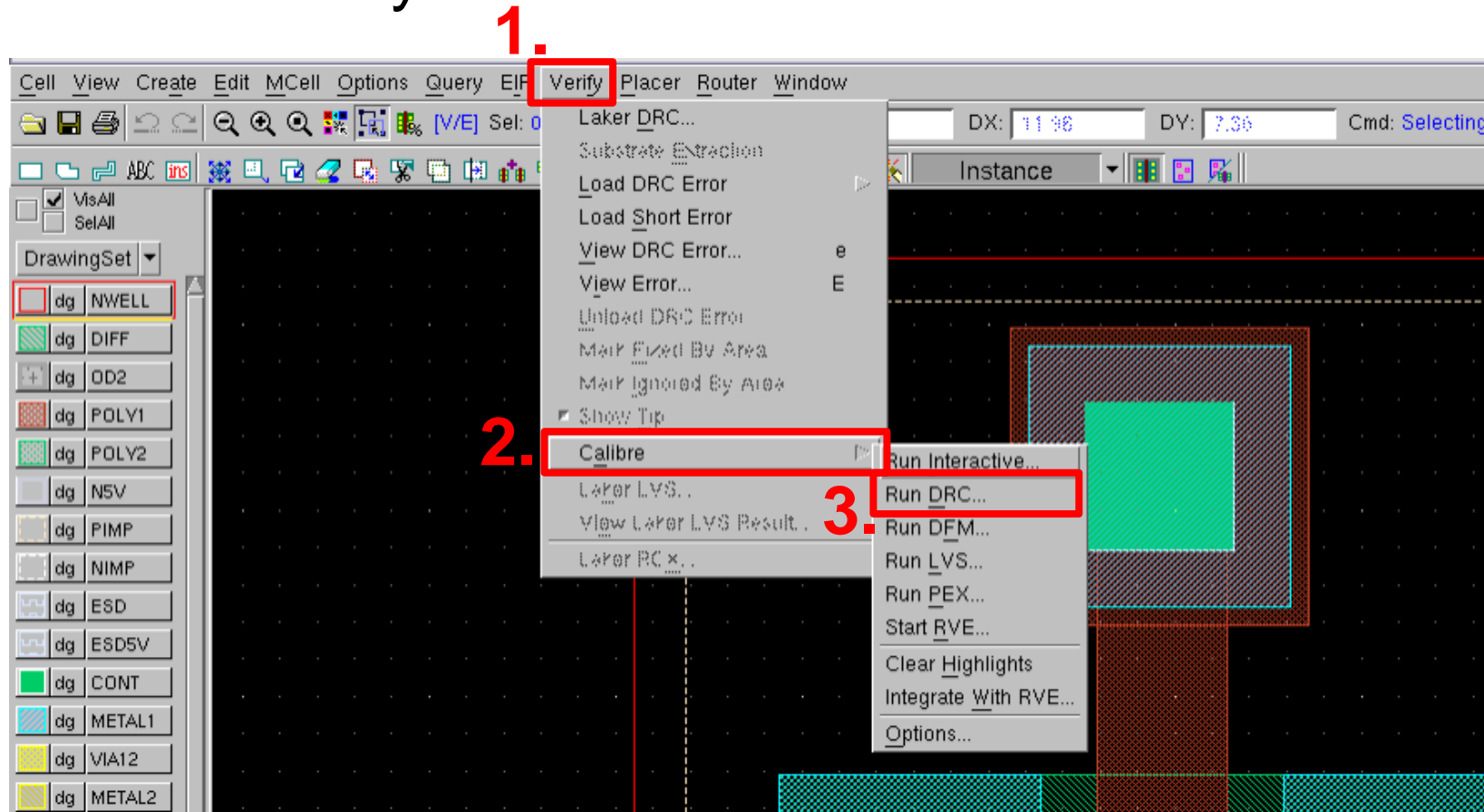


Calibre DRC Flow

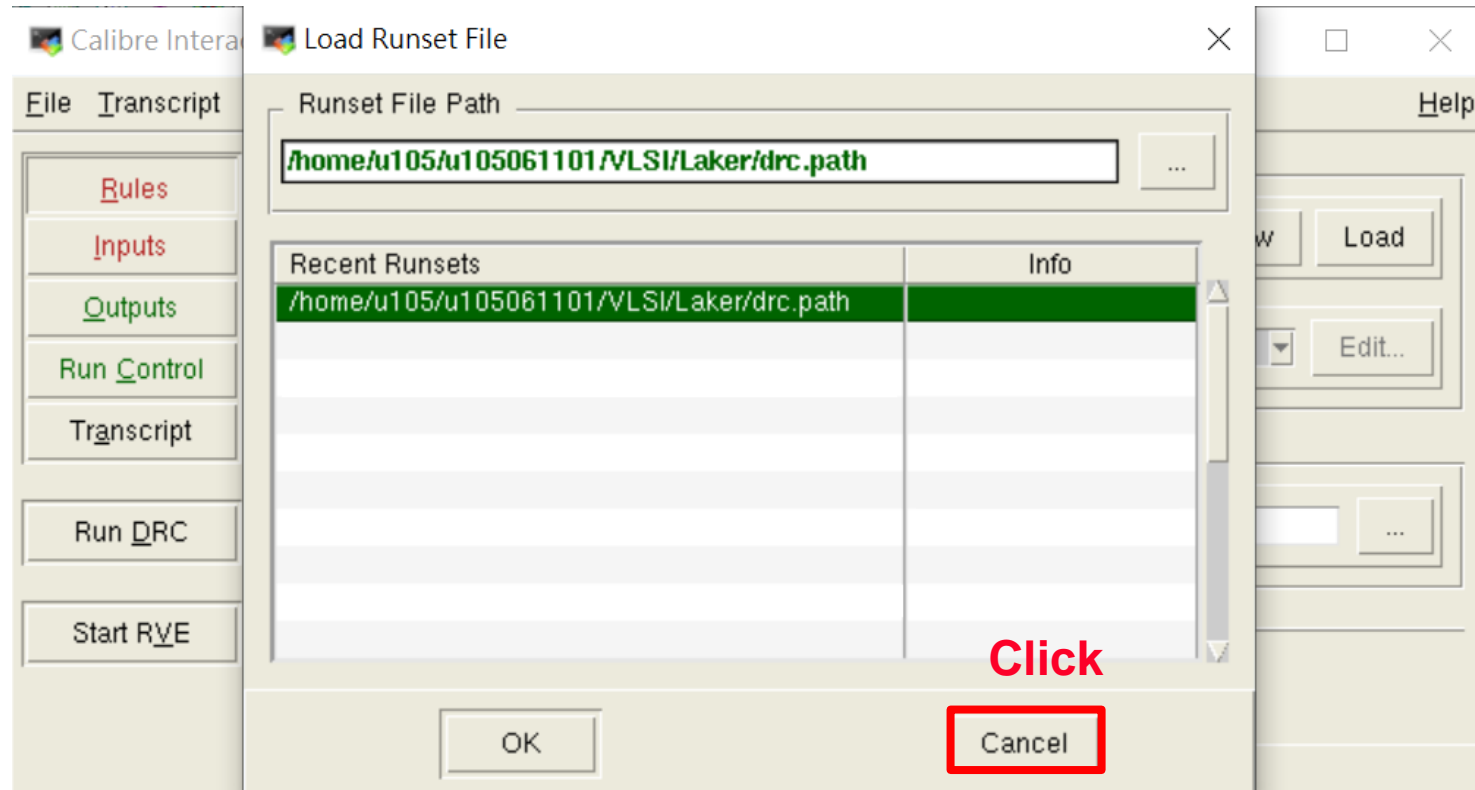
DRC

❑ Design Rule Check

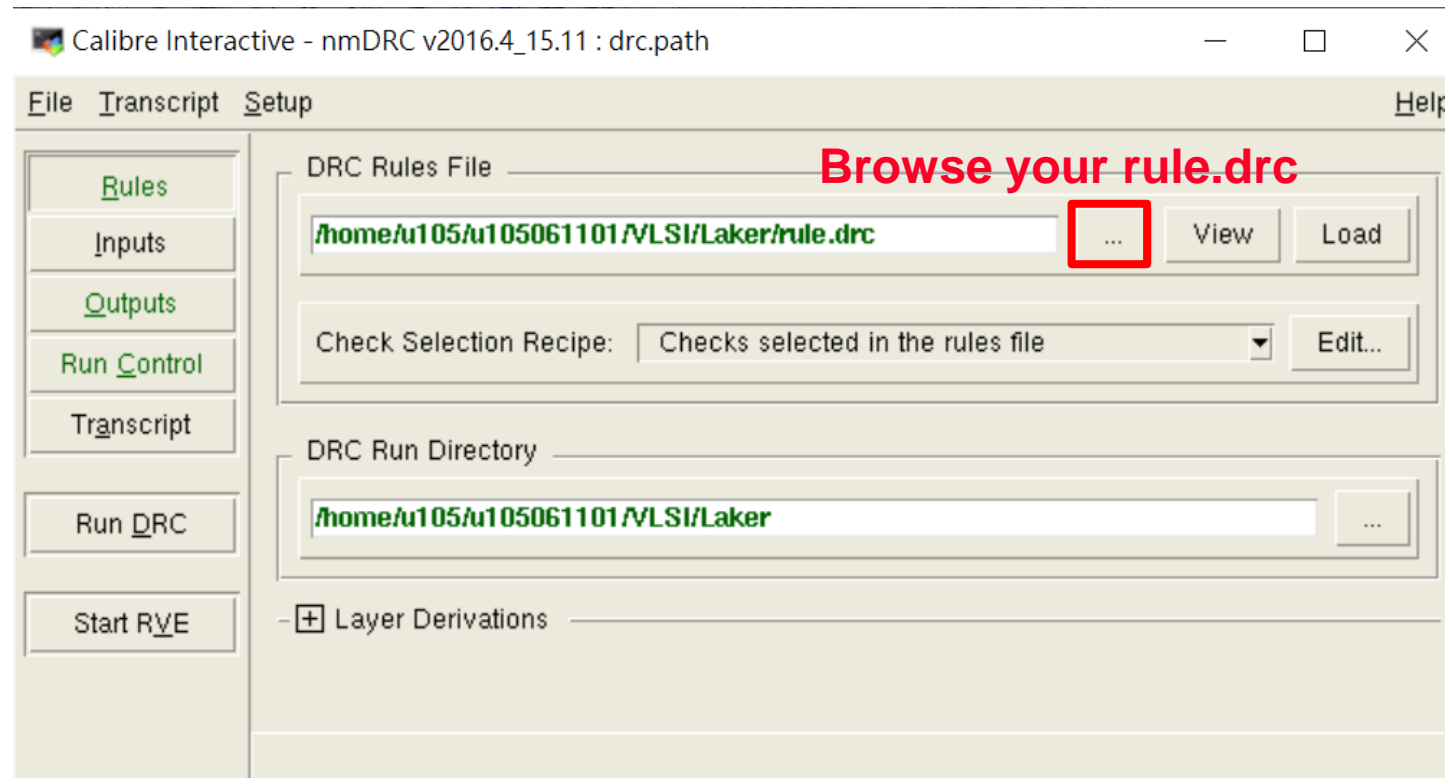
- To check if the layout violates fabrication rule



DRC

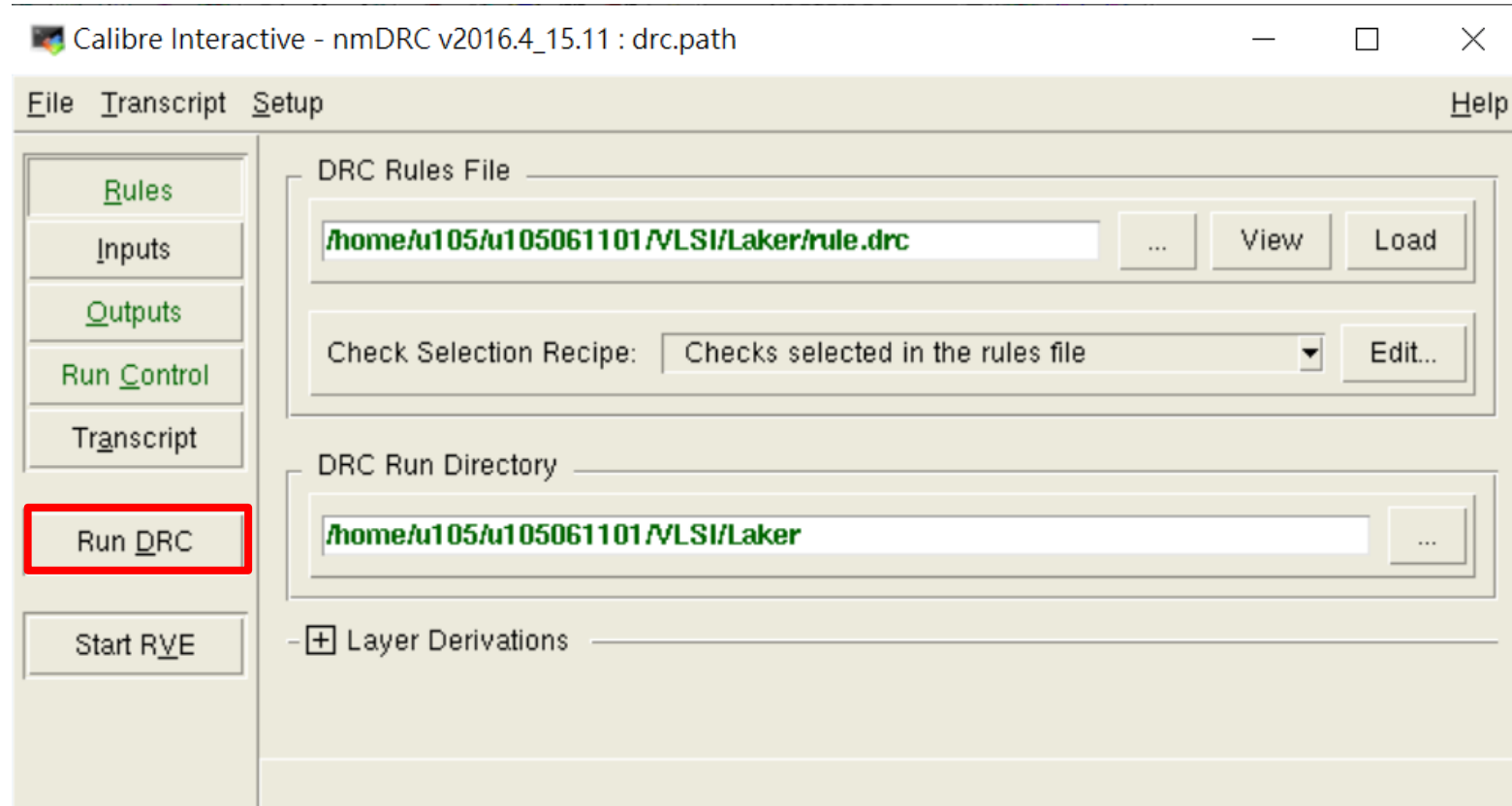


DRC – Rules



DRC – Run

❑ Run DRC



DRC – Results

Calibre - RVE v2016.4_15.11 : HW3_inv.drc.results

File View Highlight Tools Window Setup Help

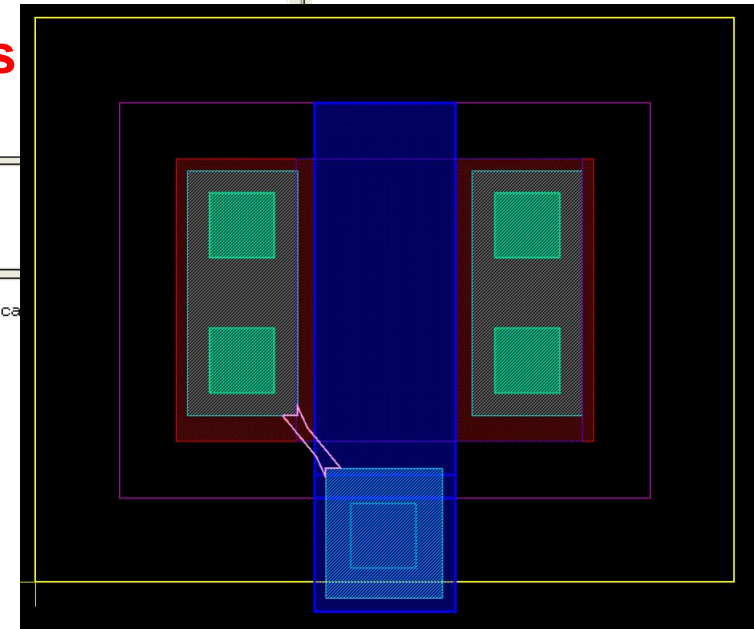
Show All HW3_inv, 2 Results (in 2 of 2 Checks)

Check / Cell	Resu
✗ Check NIMP.S7	1
✗ Check PIMP.S7	1

Rule File Pathname: /home/u105/u105061101/VLSI/Laker/_rule.drc_
Maximum N+ diffusion to the nearest P+ pick-up spacing (inside P-Well or Twell) is 20um (I/O, RAM, ROM, ca
excepted)

How many this kind mistakes
Double clicks at number will
highlight at layout

Show you the rule

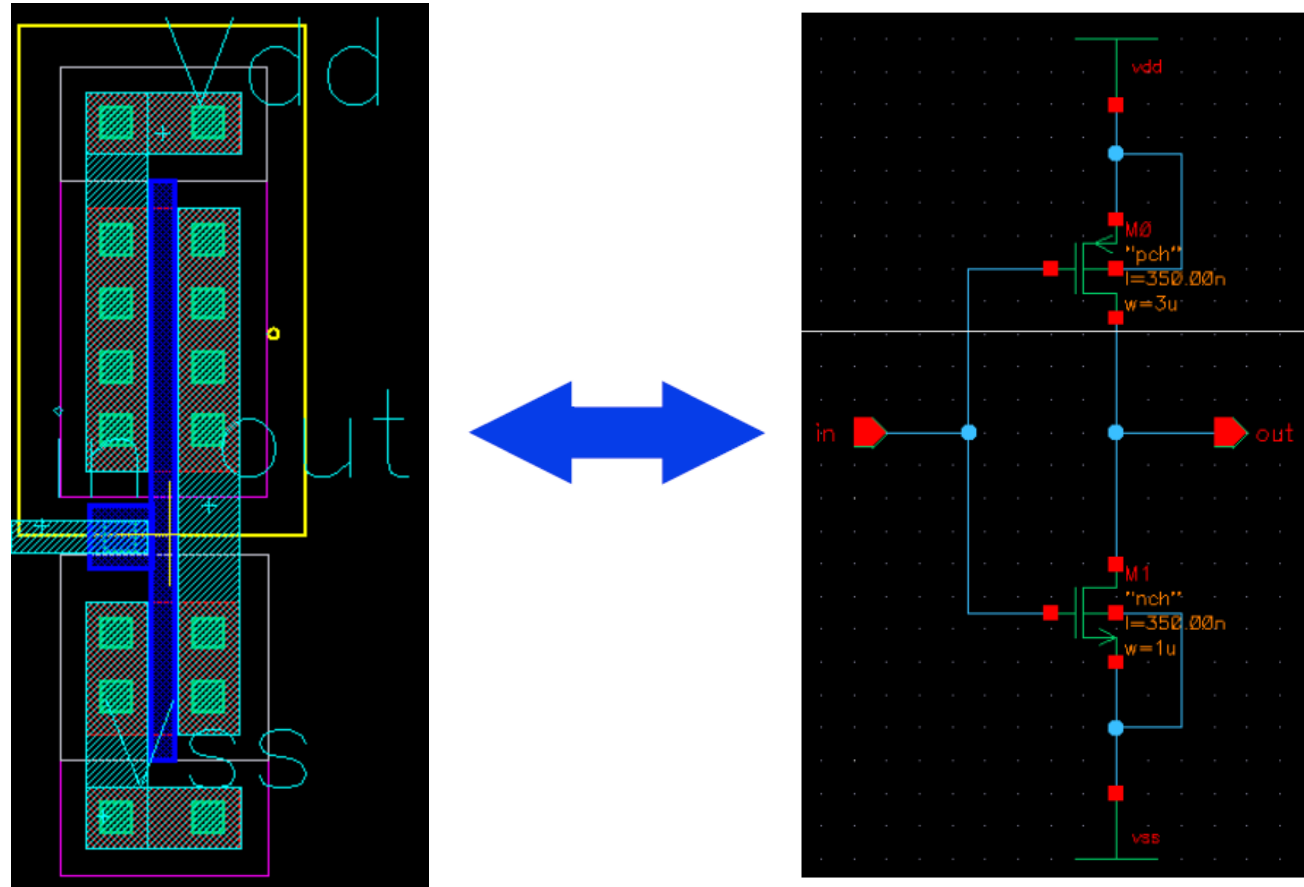


Calibre LVS Flow

LVS

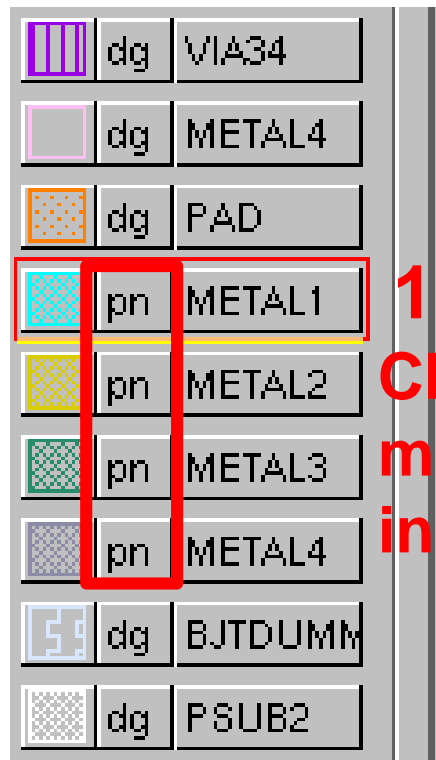
Layout v.s. Schematic

- To check whether layout and schematic are the same

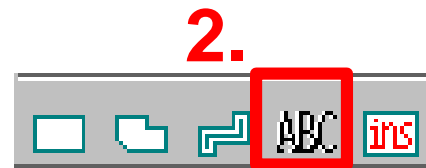


LVS – PIN (1/2)

? Create the pin

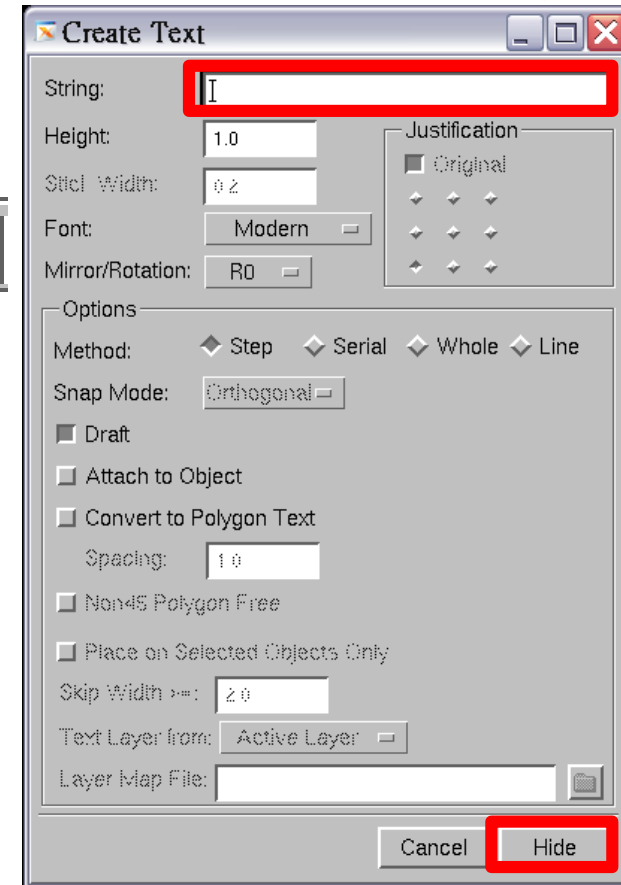


1. Choose one material in pn type



2.

3. Names of I/O or VDD or GND



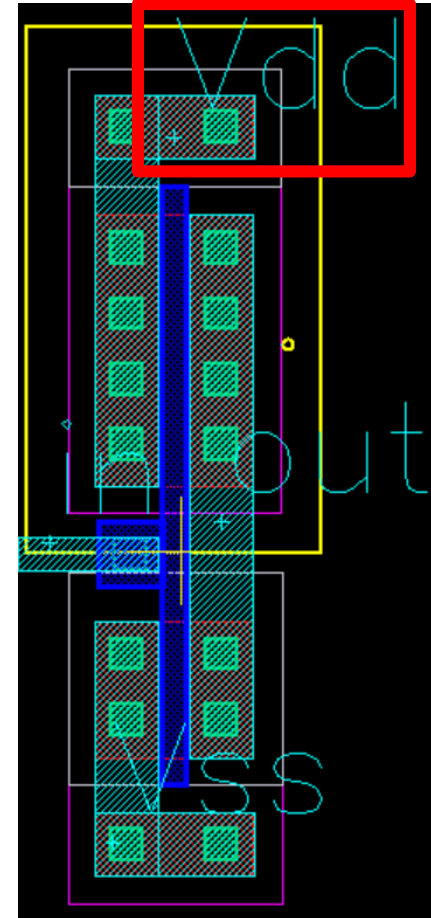
4.

LVS – PIN (2/2)

❓ Put the pin on the corresponding position



**This sign must touch
that kind of metal**



Netlist File

- ❑ The netlist has to be in SUBCKT type
- ❑ Change PM to P_18, NM to N_18

Primary Cell Name

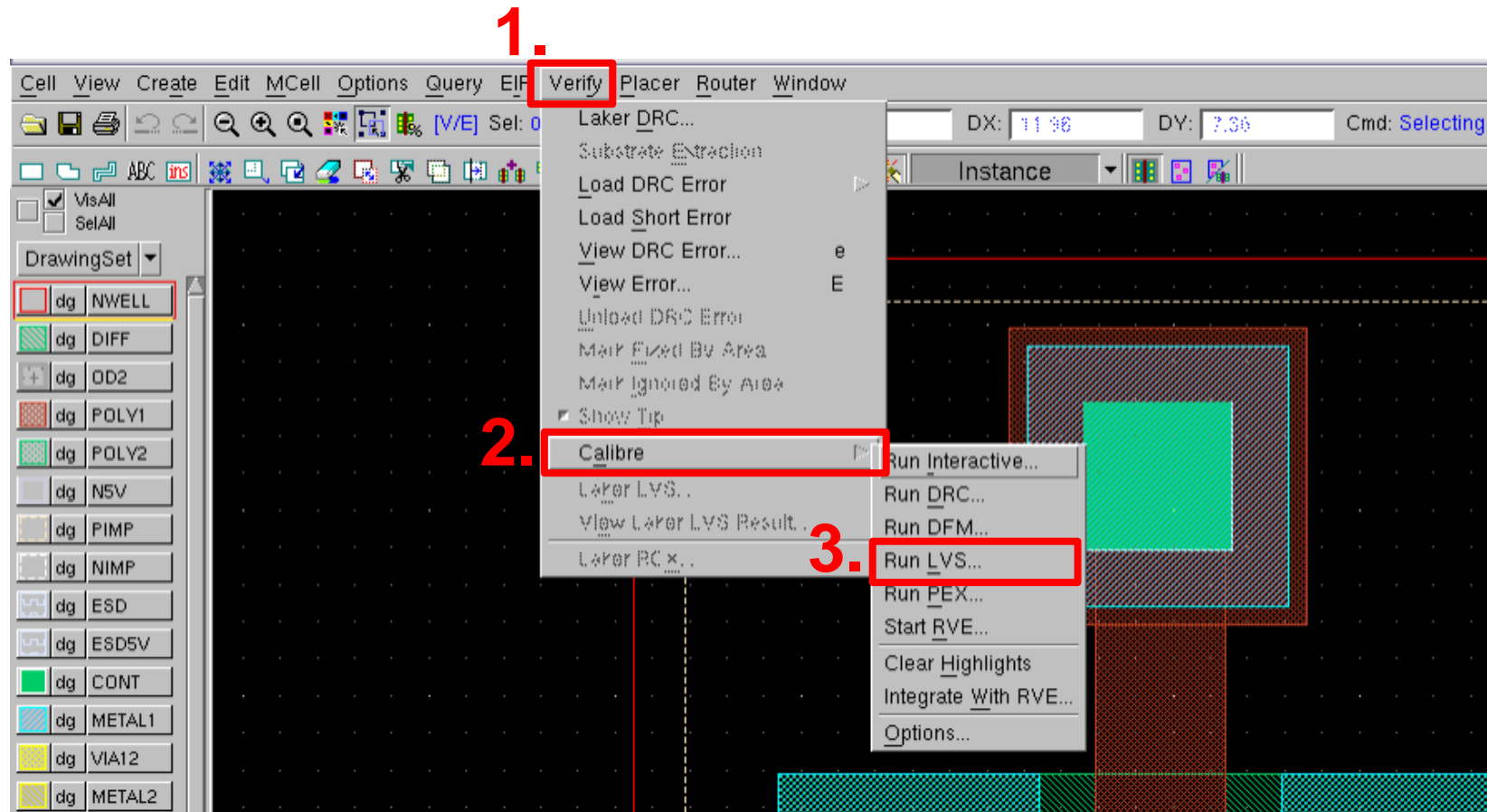
Pin (pn layer)

```
.SUBCKT inv Vdd in out Vss
*.PININFO Vin:1 Vout:0 Vdd:B Vss:B
MM1 out in Vdd Vdd PM W=2u L=0.18u m=1
MM0 out in Vss Vss NM W=1u L=0.18u m=1
.ends
```

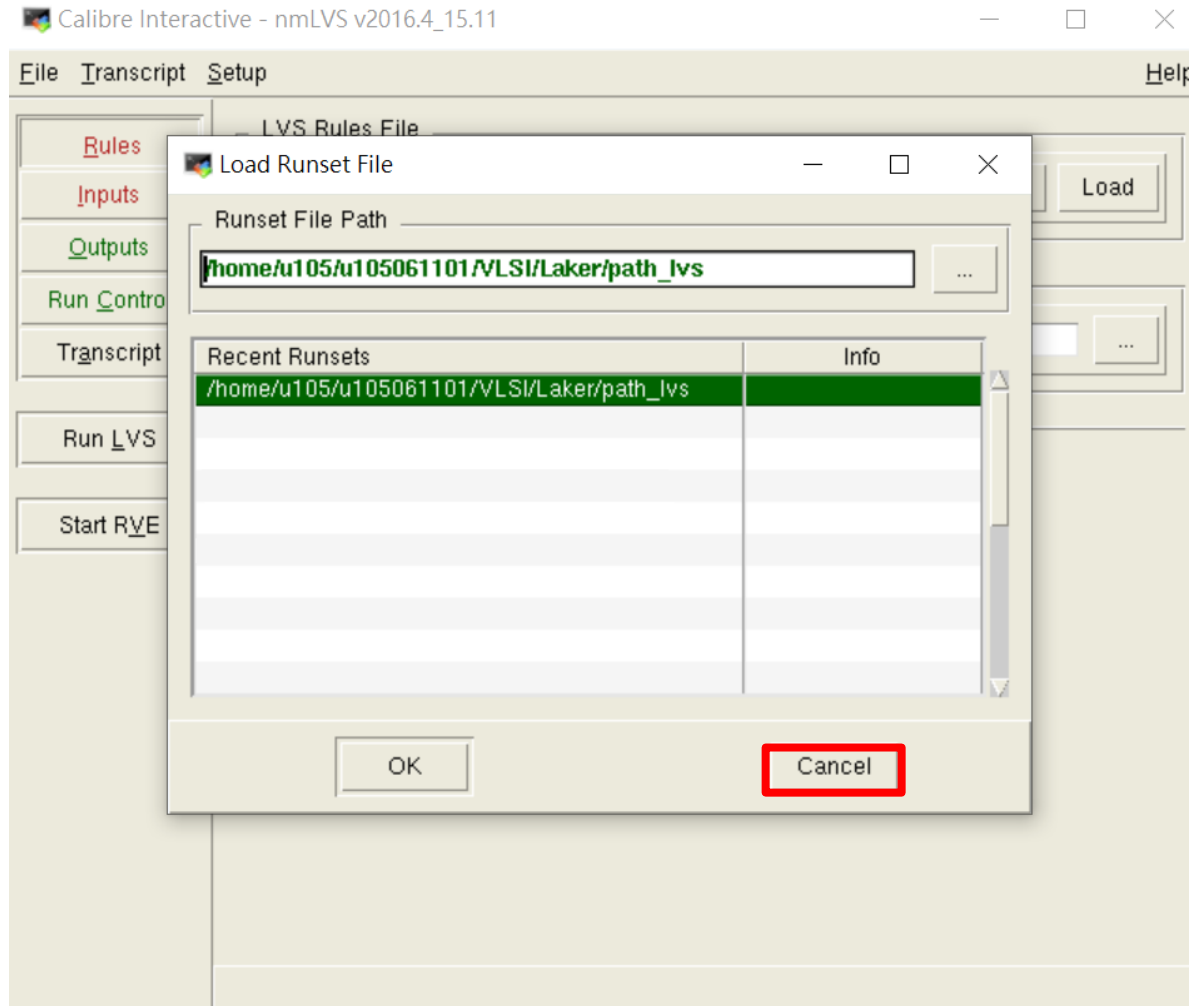
```
.SUBCKT inv Vdd in out Vss
*.PININFO Vin:1 Vout:0 Vdd:B Vss:B
MM1 out in Vdd Vdd p_18 W=2u L=0.18u m=1
MM0 out in Vss Vss n_18 W=1u L=0.18u m=1
.ends
```

LVS

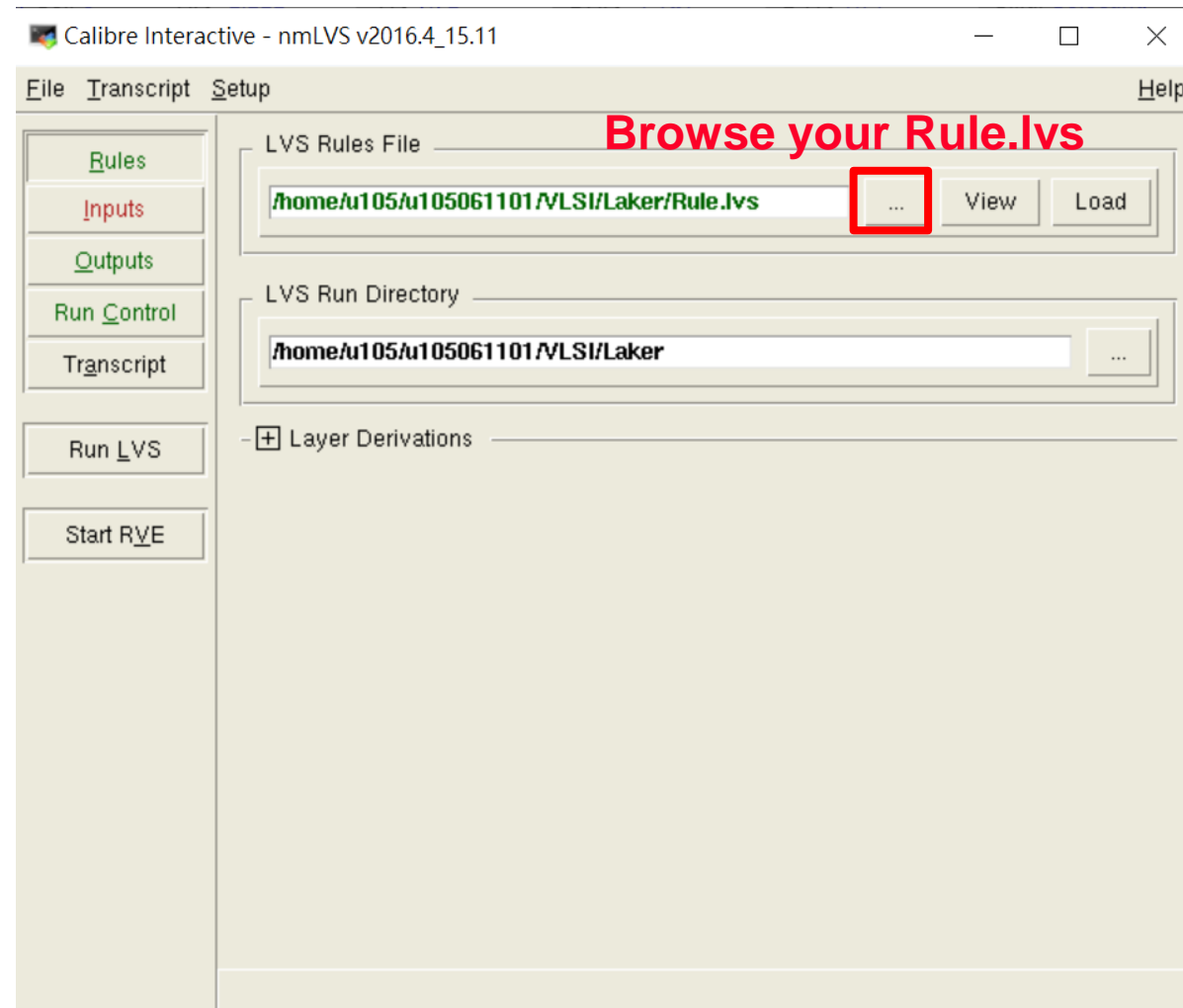
□ Verify → Calibre → Run LVS



LVS



LVS – Rules



LVS – Inputs

The screenshot shows the Calibre Interactive - nmLVS v2016.4_15.11 window. The interface includes a menu bar (File, Transcript, Setup, Help) and a left sidebar with buttons: Rules, Inputs, Outputs, Run Control, Transcript, Run LVS, and Start RVE. The main area has a 'Run:' dropdown set to 'Hierarchical' and a 'Step:' dropdown set to 'Layout vs Netlist'. Below these are tabs for 'Layout', 'Netlist', 'H-Cells', 'Signatures', and 'Waivers'. The 'Netlist' tab is active, showing a 'Format:' dropdown set to 'SPICE' and an unchecked checkbox for 'Export from schematic viewer'. The 'Spice Files:' field contains 'Final_inv_unit.src.net' and has a red box around the file name and a red arrow pointing to the '...' button. The 'Top Cell:' field contains 'Final_inv_unit' and has a red box around the text. Red annotations include: '1.' pointing to the 'Inputs' button, '2.' pointing to the 'Netlist' tab, '3. Choose your *.spi file' with a red arrow pointing to the '...' button, and '4. If the name of subckt is different with the name of Layout, fill the name of subckt here' pointing to the 'Top Cell:' field.

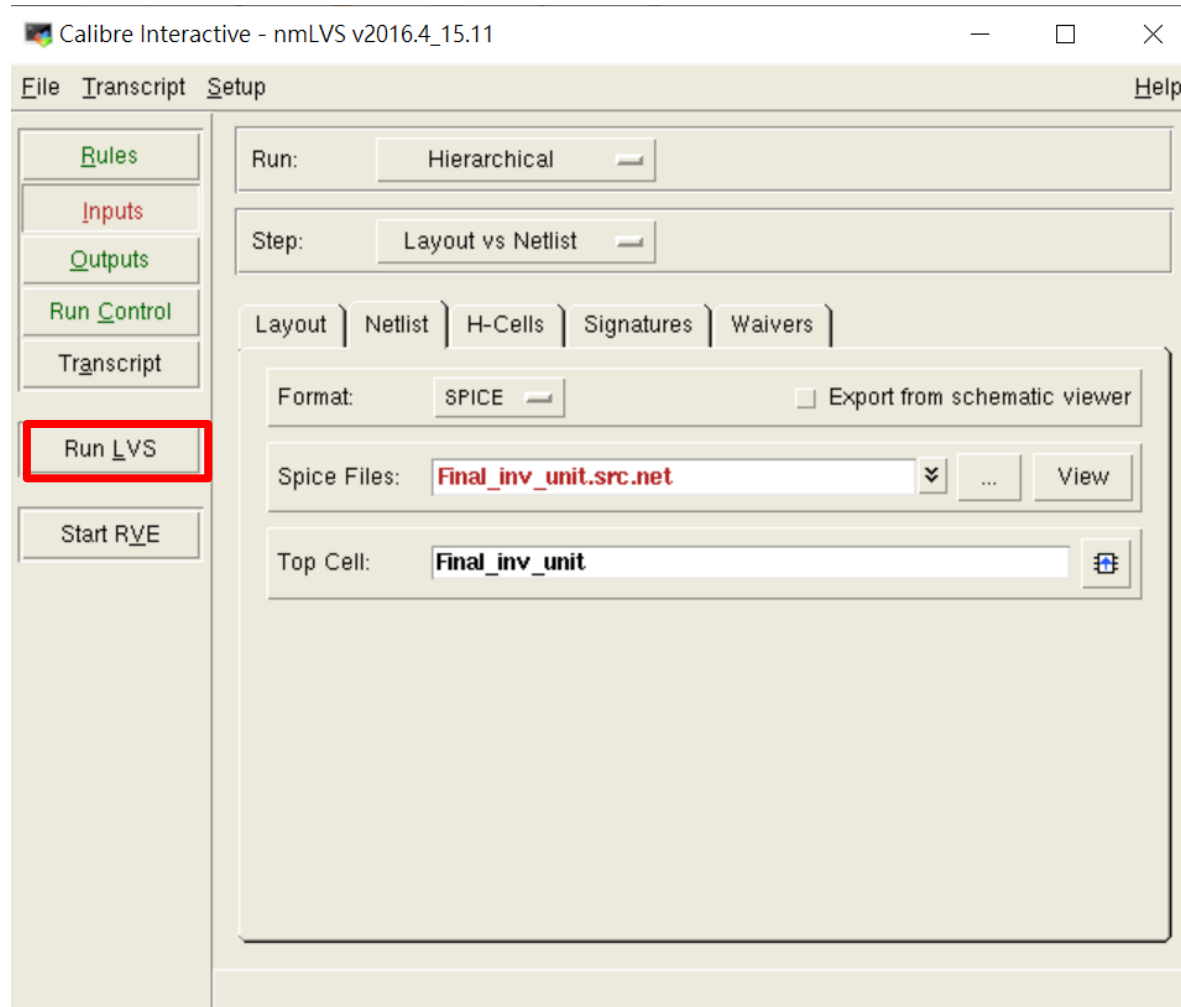
1. Inputs

2. Netlist

3. Choose your *.spi file

4. If the name of subckt is different with the name of Layout, fill the name of subckt here

LVS – Run



LVS – Results

❑ Result

- If your layout is different with subckt, you will get a big X

Calibre - RVE v2016.4_15.11 : svdb Final_inv_unit

File View Highlight Tools Window Setup Help

Search

Comparison Results

Layout Cell Type	Source Cell	Count	Net	Instances	Ports
Final_inv_unit	inv	2	4L, 4S	1L, 1S	4L, 4S

How many differences between your layout and subckt

Cell Final_inv_unit Summary (2 Discrepancies)

CELL COMPARISON RESULTS < TOP LEVEL >

INCORRECT

Error: Connectivity errors.

LAYOUT CELL NAME: Final_inv_unit
SOURCE CELL NAME: inv

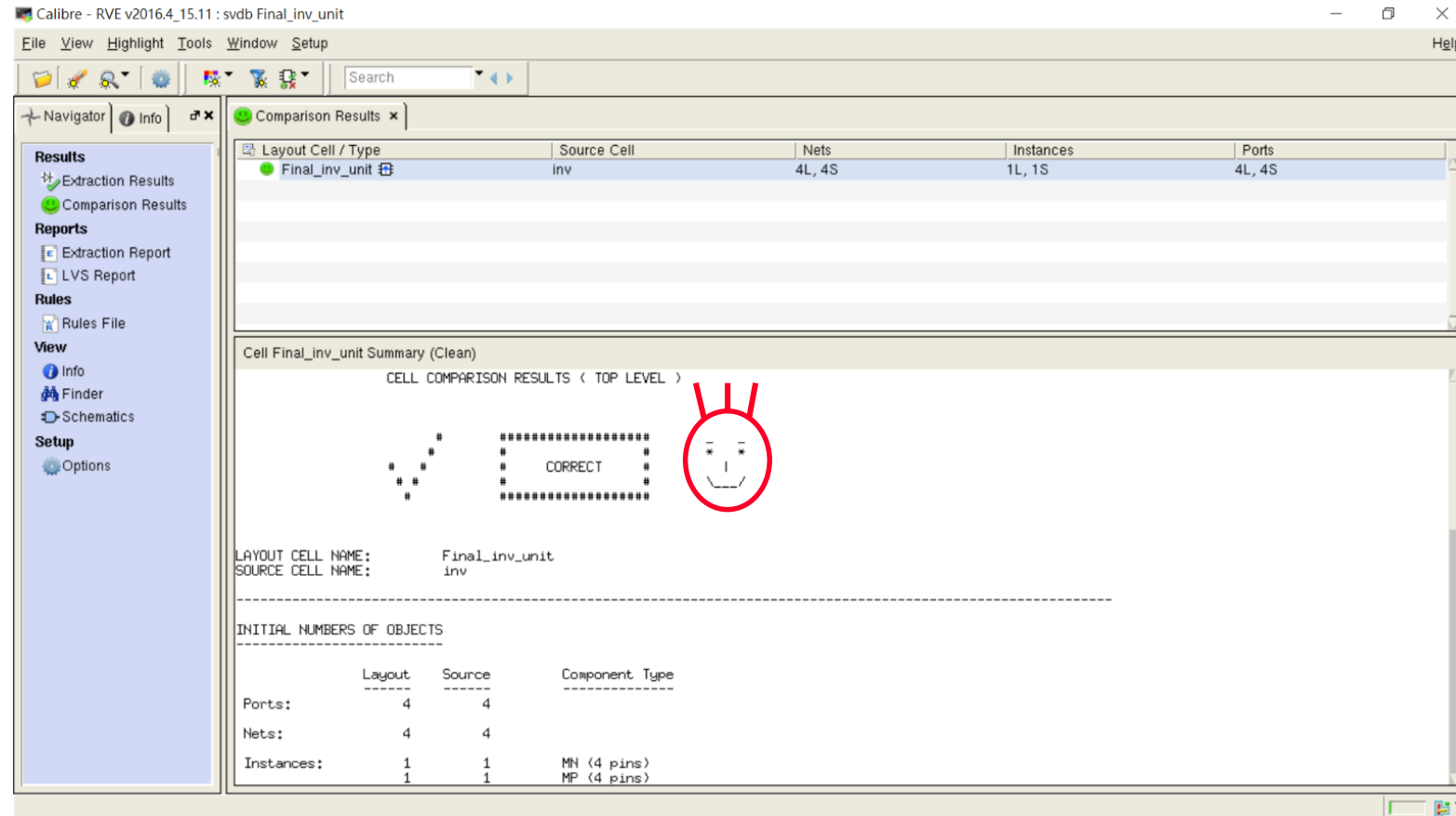
INITIAL NUMBERS OF OBJECTS

	Layout	Source	Component Type
Ports:	4	4	
Nets:	4	4	
Instances:	1	1	MN (4 pins)

LVS – Results

□ Result

- If your layout is the same as subckt, you will get a smile



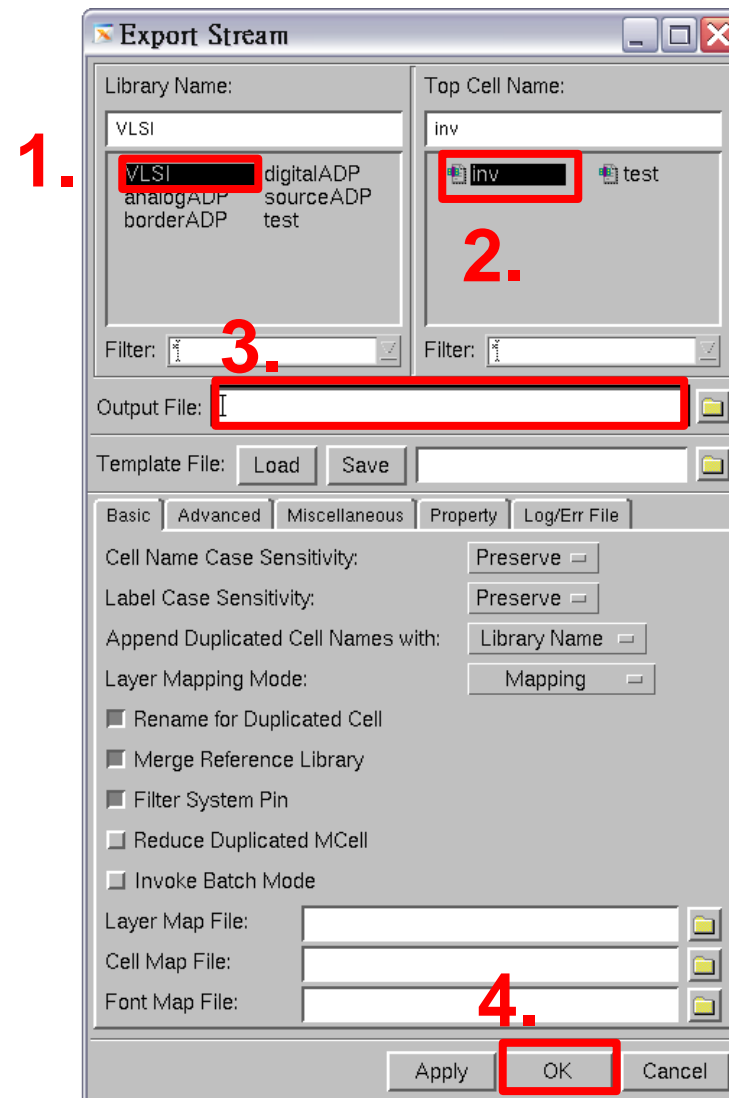
Export / Import Design

Laker – Output Design

❑ Stream Out

- File → Export → Stream
 - Choose Library
 - Choose Cell
 - Output File Name(Ex: inv.gds)
 - OK

- ❑ GDS : A file used to store the position of your layout.



Laker – Import Design

❑ Stream In

- File → Import → Stream

(It'll create a new Library)

→ Browse .gds file

→ New Library name

→ Technology file (*.tf)

→ OK

